







CC2642R ZHCSHI2H - JANUARY 2018 - REVISED MARCH 2021

CC2642R SimpleLink™ 低功耗 Bluetooth® 5.2 无线 MCU

1 特性

- 微控制器
 - 功能强大的 48MHz Arm® Cortex®-M4F 处理器
 - EEMBC CoreMark® 评分: 148
 - 352KB 系统内可编程闪存
 - 256KB ROM, 用于协议和库函数
 - 8KB 缓存 SRAM (也可作为通用 RAM 提供)
 - 80KB 超低泄漏 SRAM。SRAM 通过奇偶校验得 到保护,从而确保高度可靠运行。
 - 2 引脚 cJTAG 和 JTAG 调试
 - 支持无线 (OTA) 升级
- 具有 4KB SRAM 的超低功耗传感器控制器
 - 采样、存储和处理传感器数据
 - 独立于系统 CPU 运行
 - 快速唤醒进入低功耗运行
- TI-RTOS、驱动程序、引导加载程序、低功耗 Bluetooth® 5.2 控制器嵌入在 ROM 中,优化了应用 尺寸
- · 符合 RoHS 标准的封装
 - 7mm × 7mm RGZ VQFN48 (31 个 GPIO)
- 外设
 - 数字外设可连接至任何 GPIO
 - 4 个 32 位或 8 个 16 位通用计时器
 - 12 位 ADC、200ksps、8 通道
 - 2 个具有内部基准 DAC 的比较器 (1个连续时间比较器、1个超低功耗比较器)
 - 可编程电流源
 - 2 个异步收发器 (UART)
 - 2 个同步串行接口 (SSI) (SPI、MICROWIRE 和 TI)
 - I²C 和 I²S
 - 实时时钟 (RTC)
 - AES 128 位和 256 位加密加速计
 - ECC 和 RSA 公钥硬件加速器
 - SHA2 加速器 (包括至 SHA-512 的全套装)
 - 真随机数发生器 (TRNG)
 - 电容式检测,最多8通道
 - 集成温度和电池监控器
- 外部系统
 - 片上降压直流/直流转换器

- 低功耗
 - 有源模式 RX: 6.9 mA
 - 有源模式 TX (0dBm): 7.3mA
 - 有源模式 TX (5dBm): 9.6 mA
 - 有源模式 MCU 48MHz (CoreMark): 3.4mA (71 µ A/MHz)
 - 传感器控制器 (低功耗模式、2MHz、运行无限 环路):30.1 µ A
 - 传感器控制器,有源模式,24MHz,运行无限循 环:808 µ A
 - 待机电流:0.94 μ A(RTC 运行, 80KB RAM 和 CPU 保持)
 - 关断电流:150nA(发生外部事件时唤醒)
- 无线电部分
 - 2.4GHz 射频收发器,兼容低功耗蓝牙 5.2 与早 期 LE 规范
 - 3线、2线、1线 PTA 共存机制
 - 出色的接收器灵敏度: 蓝牙 125kbps 时(LE 编码 PHY)为 -105 dBm 1Mbps (PHY) 时为 -97dBm
 - 高达 +5dBm 的输出功率,具有温度补偿
 - 适用于符合各项全球射频规范的系统
 - EN 300 328、(欧洲)
 - EN 300 440 类别 2
 - FCC CFR47 第 15 部分
 - ARIB STD-T66(日本)
- 开发工具和软件
 - CC26x2R LaunchPad™ 开发套件
 - SimpleLink™ CC13x2 和 CC26x2 软件开发套 件 (SDK)
 - 用于简单无线电配置的 SmartRF™ Studio
 - 用于构建低功耗检测应用的 Sensor Controller Studio



2 应用

- 手机 手机电池包
- 医疗
- 楼宇自动化
 - 楼宇安防系统 运动检测器、电子智能锁、门 窗传感器、车库门系统、网关
 - HVAC 恒温器、无线环境传感器、HVAC 系 统控制器、网关
 - 防火安全系统 烟雾和热量探测器、火警控制 面板 (FACP)
 - 视频监控 IP 网络摄像头
- 电子销售终端 (EPOS) RFID 读取器
- 电网基础设施

- 工厂自动化和控制
- 3 说明

- 智能仪表 水表、燃气表、电表和热量分配表
- 电网通信 无线通信 远距离传感器应用
- 其他替代能源 能量收集
- 通信设备
 - 有线网络 无线 LAN 或 Wi-Fi 接入点、边缘路 由器
- 个人电子产品
 - 便携式电子产品 射频智能遥控器
 - 家庭影院和娱乐 智能扬声器、智能显示器、 机顶盒
 - 联网外设 消费类无线模块、指点设备、键盘
 - 游戏 电子玩具和机器人玩具
 - 可穿戴设备(非医用)-智能追踪器、智能服装

SimpleLink™ CC2642R 器件是一款 2.4GHz 无线微控制器 (MCU),支持低功耗 Bluetooth® 5.2 和专有 2.4GHz 应 用。该器件经过优化,可用于楼宇安防系统、HVAC、资产跟踪、医疗、有线网络、便携式电子产品、家庭影院和 娱乐和联网外设市场以及需要工业性能的应用中的低功耗无线通信和高级检测。该器件的突出特性包括:

- 支持 Bluetooth ® 5.2 特性: LE 编码 PHY (远距离)、LE 2Mbit PHY (高速)、广播扩展、多个广播集、 CSA#2、方向查找以及对 Bluetooth ® 4.2 和早期低功耗规范的向后兼容性和支持。
- 完全合格的 Bluetooth ® 5.2 软件协议栈 (SimpleLink™ CC13x2 和 CC26x2 软件开发套件 (SDK) 随附)。
- 延长无线应用的电池寿命,完全 RAM 保持时低待机电流为 0.94µA。
- 支持工业温度,在 105°C 下最低待机电流为 11μA。
- 通过具有快速唤醒功能的可编程、自主式超低功耗传感器控制器 CPU 实现高级检测。例如,传感器控制器能 够在 1µA 系统电流下进行 1Hz ADC 采样。
- 低 SER(软错误率) FIT(时基故障),可延长运行寿命,不会对工业市场造成干扰, SRAM 奇偶校验功能始 终开启,可防止潜在辐射事件导致的损坏。
- 软件控制的专用无线电控制器 (Arm® Cortex®-MO) 提供灵活的低功耗射频收发器功能,支持多个物理层和射频 标准(如实时定位(RTLS)技术)。
- 出色的无线电敏感度和稳健性(选择性与阻断)性能,适用于低功耗 Bluetooth®(对于 125kbps LE 编码 PHY 为 -105dBm)。

CC2642R 器件是 SimpleLink™ MCU 平台的一部分,该平台包括 Wi-Fi®、低功耗*蓝牙*、Thread、Zigbee、 Sub-1GHz MCU 和主机 MCU,它们共用一个通用、易于使用的开发环境,其中包含单核软件开发套件 (SDK)和 丰富的工具集。借助一次性集成的 SimpleLink™ 平台,可以将产品组合中的任何器件组合添加至您的设计中,从 而在设计要求变更时实现 100% 的代码重用。如需更多信息,请访问 SimpleLink™ MCU 平台。

器件信息

器件型号 ⁽¹⁾	封装	封装尺寸(标称值)
CC2642R1FRGZ	VQFN (48)	7.00mm × 7.00mm

(1) 如需所有可用器件的最新器件、封装和订购信息,请参阅节 12 中的"封装选项附录"或访问 TI 网站。



4 Functional Block Diagram

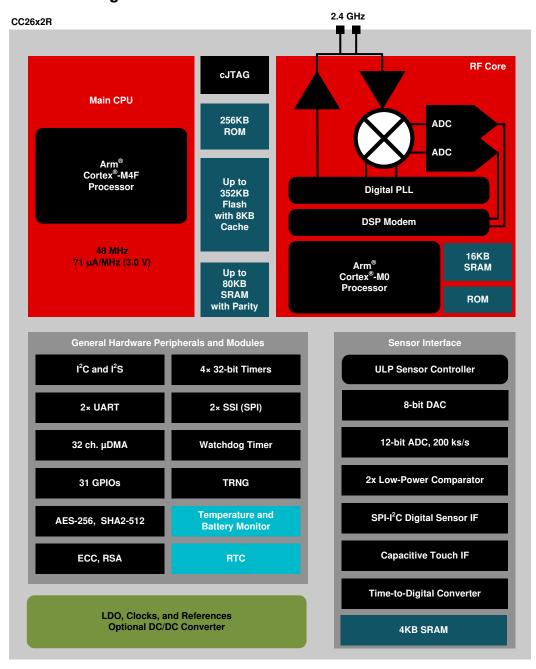


图 4-1. CC2642R Block Diagram



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5 Revision History

注:以前版本的页码可能与当前版本的页码不同

C	nanges from May 19, 2020 to March 30, 2021 (from Revision G (May 2020) to Revision H	
(N	March 2021))	Page
•	更新了整个文档中的表格、图和交叉参考的编号格式	1
•	通篇更新为蓝牙 5.2	1
•	向节 1, 特性的"无线电部分"列表中添加了 3 线、2 线和 1 线 PTA 共存机制	1
•	Changed the test condition to "Zero cycles" for the Flash sector erase time parameter in 节 8.7, Nonvolate	tile
	(Flash) Memory Characteristics	10
•	In 节 8.10: Updated data rate error tolerance (255-byte packets), Selectivity ±2MHz, Selectivity, and Imag	је
	frequency for 125 kbps (LE coded); Updated data rate error tolerance (255-byte packets), Selectivity ±2N	ΛHz,
	Selectivity, and Image frequency for 500 kbps (LE coded); Updated data rate error tolerance (37-byte	
	packets), Selectivity ±2MHz, and Selectivity ±3MHz, for 1 Mbps (LE 1M); Updated Receiver sensitivity ar	
	Selectivity, ±4MHz for 2Mbps (LE 2M)	10
•	Changed note (1) in 节 8.12.2, Wakeup Timing	10
•	Changed the frequency of the input tone for 14-bit and 15-bit mode in # 8.13.1.1	23
•	Changed the TYP Offset error and TYP Max code output voltage variation for V _{REF} = VDDS = 3.8 V, 3.0 V	V,
	and 1.8 V in 节 8.13.2.1	25
•	Added PTA description in 节 9.3, Radio (RF Core)	44
•	Added the paragraph that begins "Integrated matched filter-balun devices can be used…" in †† 10.1,	
	Reference Designs	51



6 Device Comparison

表 6-1. Device Family Overview

	衣 6-1. Devic	cc i aiiiiy	OVCIVIC	**	
DEVICE	RADIO SUPPORT	FLASH (KB)	RAM (KB)	GPIO	PACKAGE SIZE
CC1312R	Sub-1 GHz	352	80	30	RGZ (7-mm × 7-mm VQFN48)
CC1352P	Multiprotocol Sub-1 GHz Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats +20-dBm high-power amplifier	352	80	26	RGZ (7-mm × 7-mm VQFN48)
CC1352R	Multiprotocol Sub-1 GHz Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352	80	28	RGZ (7-mm × 7-mm VQFN48)
CC2642R	Bluetooth 5.2 Low Energy 2.4 GHz proprietary FSK-based formats	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2642R-Q1	Bluetooth 5.2 Low Energy	352	80	31	RTC (7-mm × 7-mm VQFN48)
CC2652R	Multiprotocol Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2652RB	Multiprotocol Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2652P	Multiprotocol Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats +19.5-dBm high-power amplifier	352	80	26	RGZ (7-mm × 7-mm VQFN48)
CC1310	Sub-1 GHz	32 - 128	16 - 20	10 - 31	RGZ (7-mm × 7-mm VQFN48) RHB (5-mm × 5-mm VQFN32) RSM (4-mm × 4-mm VQFN32)
CC1350	Sub-1 GHz Bluetooth 4.2 Low Energy	128	20	10 - 31	RGZ (7-mm × 7-mm VQFN48) RHB (5-mm × 5-mm VQFN32) RSM (4-mm × 4-mm VQFN32)
CC2640R2F	Bluetooth 5.1 Low Energy 2.4 GHz proprietary FSK-based formats	128	20	10 - 31	RGZ (7-mm × 7-mm VQFN48) RHB (5-mm × 5-mm VQFN32) RSM (4-mm × 4-mm VQFN32) YFV (2.7-mm × 2.7-mm DSBGA34)
CC2640R2F-Q1	Bluetooth 5.1 Low Energy 2.4 GHz proprietary FSK-based formats	128	20	31	RGZ (7-mm × 7-mm VQFN48)

Product Folder Links: CC2642R



7 Terminal Configuration and Functions

7.1 Pin Diagram - RGZ Package (Top View)

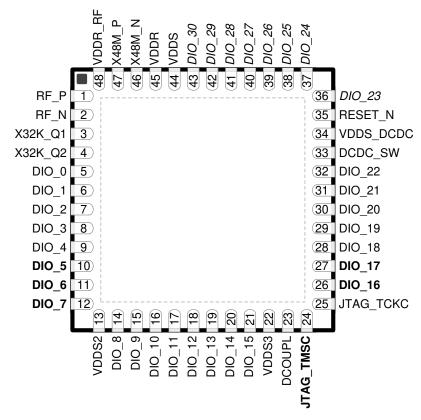


图 7-1. RGZ (7-mm×7-mm) Pinout, 0.5-mm Pitch (Top View)

The following I/O pins marked in 图 7-1 in **bold** have high-drive capabilities:

- Pin 10, DIO_5
- Pin 11, DIO 6
- Pin 12, DIO 7
- · Pin 24, JTAG TMSC
- Pin 26, DIO 16
- Pin 27, DIO_17

The following I/O pins marked in \(\bar{2} \) 7-1 in *italics* have analog capabilities:

- Pin 36, DIO 23
- Pin 37, DIO_24
- Pin 38, DIO 25
- Pin 39, DIO_26
- Pin 40, DIO_27
- Pin 41, DIO_28
- Pin 42, DIO_29
- Pin 43, DIO_30



7.2 Signal Descriptions - RGZ Package

表 7-1. Signal Descriptions - RGZ Package

PIN			-1. Signal Descrip			
NAME	NO.	- I/O	TYPE	DESCRIPTION		
DCDC_SW	33	_	Power	Output from internal DC/DC converter ⁽¹⁾		
DCOUPL	23	_	Power	For decoupling of internal 1.27 V regulated digital-supply (2)		
DIO_0	5	I/O	Digital	GPIO		
DIO_1	6	I/O	Digital	GPIO		
DIO_2	7	I/O	Digital	GPIO		
DIO_3	8	I/O	Digital	GPIO		
DIO_4	9	I/O	Digital	GPIO		
DIO_5	10	I/O	Digital	GPIO, high-drive capability		
DIO_6	11	I/O	Digital	GPIO, high-drive capability		
DIO_7	12	I/O	Digital	GPIO, high-drive capability		
DIO_8	14	I/O	Digital	GPIO		
DIO_9	15	I/O	Digital	GPIO		
DIO_10	16	I/O	Digital	GPIO		
DIO_11	17	I/O	Digital	GPIO		
DIO_12	18	I/O	Digital	GPIO		
DIO_13	19	I/O	Digital	GPIO		
DIO_14	20	I/O	Digital	GPIO		
DIO_15	21	I/O	Digital	GPIO		
DIO_16	26	I/O	Digital	GPIO, JTAG_TDO, high-drive capability		
DIO_17	27	I/O	Digital	GPIO, JTAG_TDI, high-drive capability		
DIO_18	28	I/O	Digital	GPIO		
DIO_19	29	I/O	Digital	GPIO		
DIO_20	30	I/O	Digital	GPIO		
DIO_21	31	I/O	Digital	GPIO		
DIO_22	32	I/O	Digital	GPIO		
DIO_23	36	I/O	Digital or Analog	GPIO, analog capability		
DIO_24	37	I/O	Digital or Analog	GPIO, analog capability		
DIO_25	38	I/O	Digital or Analog	GPIO, analog capability		
DIO_26	39	I/O	Digital or Analog	GPIO, analog capability		
DIO_27	40	I/O	Digital or Analog	GPIO, analog capability		
DIO_28	41	I/O	Digital or Analog	GPIO, analog capability		
DIO_29	42	I/O	Digital or Analog	GPIO, analog capability		
DIO_30	43	I/O	Digital or Analog	GPIO, analog capability		
EGP	_	_	GND	Ground - exposed ground pad ⁽³⁾		
JTAG_TMSC	24	I/O	Digital	JTAG TMSC, high-drive capability		
JTAG_TCKC	25	ı	Digital	JTAG TCKC		
RESET_N	35	I	Digital	Reset, active low. No internal pullup resistor		
RF_P	1	_	RF	Positive RF input signal to LNA during RX Positive RF output signal from PA during TX		
RF_N	2	_	RF	Negative RF input signal to LNA during RX Negative RF output signal from PA during TX		
VDDR	45	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (4) (6)		

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表 7-1. Signal Descriptions - RGZ Package (continued)

	-,	, .	2000	110_1 401490 (0011111404)
PIN		I/O TYPE		DESCRIPTION
NAME	NO.		IIFE	DESCRIPTION
VDDR_RF	48	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (5) (6)
VDDS	44	_	Power	1.8-V to 3.8-V main chip supply ⁽¹⁾
VDDS2	13	_	Power	1.8-V to 3.8-V DIO supply ⁽¹⁾
VDDS3	22	_	Power	1.8-V to 3.8-V DIO supply ⁽¹⁾
VDDS_DCDC	34	_	Power	1.8-V to 3.8-V DC/DC converter supply
X48M_N	46	_	Analog	48-MHz crystal oscillator pin 1
X48M_P	47	_	Analog	48-MHz crystal oscillator pin 2
X32K_Q1	3	_	Analog	32-kHz crystal oscillator pin 1
X32K_Q2	4	_	Analog	32-kHz crystal oscillator pin 2

- For more details, see technical reference manual listed in 节 11.2.
- Do not supply external circuitry from this pin. (2)
- EGP is the only ground connection for the device. Good electrical connection to device ground on printed circuit board (PCB) is imperative for proper device operation.
- If internal DC/DC converter is not used, this pin is supplied internally from the main LDO.
- If internal DC/DC converter is not used, this pin must be connected to VDDR for supply from the main LDO.
- Output from internal DC/DC and LDO is trimmed to 1.68 V.

7.3 Connections for Unused Pins and Modules

表 7-2. Connections for Unused Pins

FUNCTION	SIGNAL NAME	PIN NUMBER	ACCEPTABLE PRACTICE ⁽¹⁾	PREFERRED PRACTICE ⁽¹⁾
GPIO	DIO_n	5 - 12 14 - 21 26 - 32 36 - 43	NC or GND	NC
32.768-kHz crystal	X32K_Q1	3	NC or GND	NC
32.700-KHZ CI yStai	X32K_Q2	4	- NC OF GND	INC
DC/DC converter ⁽²⁾	DCDC_SW	33	NC	NC
DO/DC converter	VDDS_DCDC	34	VDDS	VDDS

- NC = No connect
- When the DC/DC converter is not used, the inductor between DCDC_SW and VDDR can be removed. VDDR and VDDR_RF must still be connected and the 22 uF DCDC capacitor must be kept on the VDDR net.



8 Specifications

8.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

			MIN	MAX	UNIT
VDDS ⁽³⁾	Supply voltage		- 0.3	4.1	V
	Voltage on any digital p	pin ⁽⁴⁾	- 0.3	VDDS + 0.3, max 4.1	V
	Voltage on crystal oscillator pins, X32K_Q1, X32K_Q2, X48M_N and X48M_P		- 0.3	VDDR + 0.3, max 2.25	V
	Voltage on ADC input	Voltage scaling enabled	- 0.3	VDDS	V
V _{in}		Voltage scaling disabled, internal reference	- 0.3	1.49	
		Voltage scaling disabled, VDDS as reference	- 0.3	VDDS / 2.9	
	Input level, RF pins			5	dBm
T _{stg}	Storage temperature		- 40	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

8.2 ESD Ratings

				VALUE	UNIT
Electrostatic	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	All pins	±2000	V
V _{ESD}	discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	All pins	±500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process

8.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Operating junction temperature	- 40	105	°C
Operating supply voltage (VDDS)	1.8	3.8	V
Rising supply voltage slew rate	0	100	mV/μs
Falling supply voltage slew rate ⁽¹⁾	0	20	mV/μs

⁽¹⁾ For small coin-cell batteries, with high worst-case end-of-life equivalent source resistance, a 22-μF VDDS input capacitor must be used to ensure compliance with this slew rate.

Product Folder Links: CC2642R

⁽²⁾ All voltage values are with respect to ground, unless otherwise noted.

⁽³⁾ VDDS_DCDC, VDDS2 and VDDS3 must be at the same potential as VDDS.

⁽⁴⁾ Including analog capable DIOs.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process

8.4 Power Supply and Modules

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNIT
VDDS Power-on-Reset (POR) threshold			1.1 - 1.55		V
VDDS Brown-out Detector (BOD) (1)	Rising threshold		1.77		V
VDDS Brown-out Detector (BOD), before initial boot (2)	Rising threshold		1.70		V
VDDS Brown-out Detector (BOD) (1)	Falling threshold		1.75		V

For boost mode (VDDR =1.95 V), TI drivers software initialization will trim VDDS BOD limits to maximum (approximately 2.0 V) Brown-out Detector is trimmed at initial boot, value is kept until device is reset by a POR reset or the RESET_N pin (1)

⁽²⁾



8.5 Power Consumption - Power Modes

When measured on the CC26x2REM-7ID reference design with T_c = 25 °C, V_{DDS} = 3.0 V with DC/DC enabled unless otherwise noted.

PARAMETER		TEST CONDITIONS	TYP	UNIT
Core Curr	ent Consumption			
	Reset and Shutdown	Reset. RESET_N pin asserted or VDDS below power-on-reset threshold	150	nA
		Shutdown. No clocks running, no retention	150	
	Standby without cache	RTC running, CPU, 80KB RAM and (partial) register retention. RCOSC_LF	0.94	μΑ
	retention	RTC running, CPU, 80KB RAM and (partial) register retention XOSC_LF	1.09	μΑ
I _{core}	Standby	RTC running, CPU, 80KB RAM and (partial) register retention. RCOSC_LF	3.2	μA
	with cache retention	RTC running, CPU, 80KB RAM and (partial) register retention. XOSC_LF	3.3	μΑ
	Idle	Supply Systems and RAM powered RCOSC_HF	675	μΑ
	Active	MCU running CoreMark at 48 MHz RCOSC_HF	3.39	mA
Periphera!	Current Consumption(1)	2)	<u>'</u>	
	Peripheral power domain	Delta current with domain enabled	97.7	
	Serial power domain	Delta current with domain enabled	7.2	
	RF Core	Delta current with power domain enabled, clock enabled, RF core idle	210.9	
	μDMA	Delta current with clock enabled, module is idle	63.9	
	Timers	Delta current with clock enabled, module is idle ⁽⁵⁾	81.0	
I _{peri}	I2C	Delta current with clock enabled, module is idle	10.1	μΑ
	128	Delta current with clock enabled, module is idle	26.3	
	SSI	Delta current with clock enabled, module is idle	82.9	
	UART	Delta current with clock enabled, module is idle ⁽³⁾	167.5	
	CRYPTO (AES)	Delta current with clock enabled, module is idle ⁽⁴⁾	25.6	
	PKA	Delta current with clock enabled, module is idle	84.7	
	TRNG	Delta current with clock enabled, module is idle	35.6	
Sensor Co	ontroller Engine Consump	tion	1	
	Active mode	24 MHz, infinite loop	808.5	
I _{SCE}	Low-power mode	2 MHz, infinite loop	30.1	μΑ

- Adds to core current I_{core} for each peripheral unit activated. I_{peri} is not supported in Standby or Shutdown modes. Only one UART running Only one SSI running
- (1) (2)
- (3)
- (4)
- Only one GPTimer running

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8.6 Power Consumption - Radio Modes

When measured on the reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V with DC/DC enabled unless otherwise noted.

	PARAMETER	TEST CONDITIONS	TYP	UNIT
Ra	adio receive current	2440 MHz	6.9	mA
Radio transmit current	0 dBm output power setting 2440 MHz	7.3	mA	
2.4	.4 GHz PA (BLE)	+5 dBm output power setting 2440 MHz	9.6	mA

8.7 Nonvolatile (Flash) Memory Characteristics

Over operating free-air temperature range and V_{DDS} = 3.0 V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Flash sector size			8		KB
Supported flash erase cycles before failure, full bank ⁽¹⁾ ⁽⁵⁾		30			k Cycles
Supported flash erase cycles before failure, single sector ⁽²⁾		60			k Cycles
Maximum number of write operations per row before sector erase ⁽³⁾				83	Write Operations
Flash retention	105 °C	11.4			Years at 105 °C
Flash sector erase current	Average delta current		10.7		mA
Flash sector erase time ⁽⁴⁾	Zero cycles		10		ms
Flash write current	Average delta current, 4 bytes at a time		6.2		mA
Flash write time ⁽⁴⁾	4 bytes at a time		21.6		μs

- (1) A full bank erase is counted as a single erase cycle on each sector
- (2) Up to 4 customer-designated sectors can be individually erased an additional 30k times beyond the baseline bank limitation of 30k cycles
- (3) Éach wordline is 2048 bits (or 256 bytes) wide. This limitation corresponds to sequential memory writes of 4 (3.1) bytes minimum per write over a whole wordline. If additional writes to the same wordline are required, a sector erase is required once the maximum number of write operations per row is reached.
- 4) This number is dependent on Flash aging and increases over time and erase cycles
- (5) Aborting flash during erase or program modes is not a safe operation.

8.8 Thermal Resistance Characteristics

		PACKAGE	
	THERMAL METRIC ⁽¹⁾	RGZ (VQFN)	UNIT
		48 PINS	
R ₀ JA	Junction-to-ambient thermal resistance	23.4	°C/W ⁽²⁾
R _{θ JC(top)}	Junction-to-case (top) thermal resistance	13.3	°C/W ⁽²⁾
R _{θ JB}	Junction-to-board thermal resistance	8.0	°C/W ⁽²⁾
ΨJT	Junction-to-top characterization parameter	0.1	°C/W ⁽²⁾
ψ ЈВ	Junction-to-board characterization parameter	7.9	°C/W ⁽²⁾
R _{θ JC(bot)}	Junction-to-case (bottom) thermal resistance	1.7	°C/W ⁽²⁾

- (1) For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.
- (2) °C/W = degrees Celsius per watt.



8.9 RF Frequency Bands

Over operating free-air temperature range (unless otherwise noted).

PARAMETER	MIN	TYP MAX	UNIT
Frequency bands	2360	2500	MHz



8.10 Bluetooth Low Energy - Receive (RX)

When measured on the CC26x2REM-7ID reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

Receiver saturation Differential mode. BER = 10 ⁻³ >5 dBi Difference between the incoming carrier frequency of the internal by generated darrier frequency. Data rate error tolerance Difference between incoming data rate and the internal by generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internal by generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internal by generated data rate (37-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer in channel, ERR = 10 ⁻³ Selectivity, ±1 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±1 MHz, ERR = 10 ⁻³ Selectivity, ±2 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, ERR = 10 ⁻³ Selectivity, ±2 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, ERR = 10 ⁻³ Selectivity, ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, ERR = 10 ⁻³ Selectivity, ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, ERR = 10 ⁻³ Selectivity, ±6 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, ERR = 10 ⁻³ Selectivity, ±6 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±5 MHz, ERR = 10 ⁻³ Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±5 MHz, ERR = 10 ⁻³ Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±5 MHz, ERR = 10 ⁻³ Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±5 MHz, ERR = 10 ⁻³ Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±5 MHz, ERR = 10 ⁻³ Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±7 MHz, ERR = 10 ⁻³ Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±6 MHz, ERR = 10 ⁻³ Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±6 MHz, ERR =	PARAMETER	TEST CONDITIONS	MIN TYP MA	XX UNIT
Receiver saturation Differential mode. BER = 10 ⁻³ >5 dBi Difference between the incoming carrier frequency error tolerance Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (25-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Selectivity, ±2 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 ⁻³ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 ⁻³ Selectivity, ±3 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±6 MHz, BER = 10 ⁻³ Wanted signal at - 79 dBm, modulated interferer at ±7 MHz, BER = 10 ⁻³ Wanted signal at - 79 dBm, modulated interferer at ±7 MHz, BER = 10 ⁻³ Wanted signal at - 79 dBm, modulated interferer at ±7 MHz, BER = 10 ⁻³ Wanted signal at - 79 dBm, modulated interferer at ±7 MHz, BER = 10 ⁻³ Wanted signal at - 79 dBm, modulated interferer at ±7 MHz, BER = 10 ⁻³ Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at targe frequency, BER = 10 ⁻³ Selectivity, Image frequency ⁽¹⁾ Differential mode. BER = 10 ⁻³ > 5 dBm, Mtz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at mage frequency, BER = 10 ⁻³ > 5 dBm, Mtz ⁽¹⁾ Difference between incoming data rate and the internally generated data rate (125 kbps (LE Coded)			
Difference between the incoming carrier frequency and the internally generated carrier frequency and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Co-channel rejection ⁽¹⁾ Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer in channel, BER = 10 - 3 Selectivity, ±2 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Selectivity, ±3 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±6 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±6 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±8 ±7 MHz, BER = 10 - 3 Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at image frequency, BER = 10 - 3 Selectivity, Image frequency ⁽²⁾ Difference between the incoming carrier frequency, BER = 10 - 3 Selectivity, Image frequency the modulated interferer at ±1 MHz is the Co-channel - 1 MHz. Wanted signal at - 79 dBm, modulated interferer at 1 MHz is the Co-channel - 1 MHz. Wanted signal at - 79 dBm, modulated interferer at 1 MHz is the Co-channel - 1 MHz. Wanted signal at - 79 dBm, modulated interferer at 1 MHz is the Co-channel - 1 MHz. Wanted signal at - 79 dBm, modulated interferer at 1	Receiver sensitivity	Differential mode. BER = 10 ⁻³	- 105	dBm
frequency error tolerance frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (27-byte packets) Co-channel rejection(1) Wanted signal at - 79 dBm, modulated interferer in channel, BER = 10 - 3 Selectivity, ±1 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±1 MHz, BER = 10 - 3 Selectivity, ±2 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Selectivity, ±3 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, ±4 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, ±4 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, ±6 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, Image frequency(1) Note that Image frequency +1 MHz is the Co-channel +1 MHz. Wanted signal at - 79 dBm, modulated interferer at 1 MHz from image frequency, BER = 10 - 3 Selectivity, Image frequency +1 Differential mode. BER = 10 - 3 Note that Image frequency +1 MHz is the Co-channel +1 MHz. Wanted signal at - 79 dBm, modulated interferer at 1 MHz from image frequency, BER = 10 - 3 Solectivity, Image frequency +1 Differential mode. BER = 10 - 3 Solectivity, Image frequency +1 Differential mode. BER = 10 - 3 Solectivity, Image frequency +1 Differential mode. BER = 10 - 3 Solectivity, Image frequency +1 Differential mode. BER = 10 - 3 Solectivity, Image frequency +1 Differential mode. BER = 10 - 3 Solectivity, Image frequency +1 Differential mo	Receiver saturation	Differential mode. BER = 10 ⁻³	>5	dBm
Data rate error tolerance internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at -79 dBm, modulated interferer in channel, BER = 10 -3 Selectivity, ±1 MHz(1) Wanted signal at -79 dBm, modulated interferer at ±1 MHz, BER = 10 -3 Selectivity, ±2 MHz(1) Wanted signal at -79 dBm, modulated interferer at ±2 MHz, BER = 10 -3 Selectivity, ±3 MHz(1) Wanted signal at -79 dBm, modulated interferer at ±3 MHz, BER = 10 -3 Selectivity, ±4 MHz(1) Wanted signal at -79 dBm, modulated interferer at ±4 MHz, BER = 10 -3 Selectivity, ±4 MHz(1) Wanted signal at -79 dBm, modulated interferer at ±4 MHz, BER = 10 -3 Selectivity, ±6 MHz(1) Wanted signal at -79 dBm, modulated interferer at ±4 MHz, BER = 10 -3 Selectivity, ±6 MHz(1) Wanted signal at -79 dBm, modulated interferer at ±4 MHz, BER = 10 -3 Selectivity, ±7 MHz Wanted signal at -79 dBm, modulated interferer at ±2 MHz, BER = 10 -3 Selectivity, image frequency. Wanted signal at -79 dBm, modulated interferer at ±3 2 MHz, BER = 10 -3 Wanted signal at -79 dBm, modulated interferer at ±3 MHz, BER = 10 -3 Wanted signal at -79 dBm, modulated interferer at image frequency. BER = 10 -3 Wanted signal at -79 dBm, modulated interferer at image frequency. BER = 10 -3 Wanted signal at -79 dBm, modulated interferer at image frequency. BER = 10 -3 Selectivity, Image frequency ±1 MHz(1) Wanted signal at -79 dBm, modulated interferer at image frequency at image frequency. BER = 10 -3 Selectivity, Image frequency ±1 MHz(1) Differential mode. BER = 10 -3 Selectivity, image frequency ±1 MHz(1) Differential mode. BER = 10 -3 Selectivity, image frequency ±1 Differential mode. BER = 10 -3 Selectivity, image frequency ±1 Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 -3 Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 -3 Wanted signal at -72 dBm, modulated interferer in	Frequency error tolerance	frequency and the internally generated carrier	> (- 300 / 300)	kHz
Data rate error tolerance internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at - 79 dBm, modulated interferer in channel, BER = 10 - 3 Selectivity, ±1 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±1 MHz, BER = 10 - 3 Selectivity, ±2 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Selectivity, ±3 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Selectivity, ±3 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Selectivity, ±4 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±4 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±6 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±2 ±6 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±2 ±7 MHz, BER = 10 - 3 Selectivity, Image frequency(1) Wanted signal at - 79 dBm, modulated interferer at image frequency, BER = 10 - 3 Note that Image frequency ±1 MHz, BER = 10 - 3 Note that Image frequency ±1 MHz, BER = 10 - 3 Note that Image frequency ±1 MHz is the Co-channel - 1 MHz. Wanted signal at - 79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 - 3 Solectivity, Image frequency ±1 MHz, BER = 10 - 3 Solectivity image frequency ±1 MHz, BER = 10 - 3 Solectiver sensitivity Differential mode. BER = 10 - 3 Solectiver sensitivity Differential mode. BER = 10 - 3 Solectiver sensitivity Difference between the incoming carrier frequency and the internally generated data rate (37-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte pac	Data rate error tolerance		> (- 320 / 240)	ppm
Selectivity, ±1 MHz ⁽¹⁾ Wanted signal at -79 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ±3 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ±3 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ±4 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ±4 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ≥ ±6 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ≥ ±7 MHz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at ±1 4 Mz, BER = 10 ⁻³ db wanted signal at -79 dBm, modulated interferer at wanted wanted signal at -79 dBm, modulated interferer at ±1 MHz is the Co-channel -1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz is the Co-channel -1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz is the Co-dhannel -1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz is the Co-dhannel -1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz is the Co-dhannel repertor tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) wanted signal at -72 dBm, modulated interferer in channel, BER = 10 ⁻³ wanted signal at -72 dBm, modulated interferer at ±1 MHz. BER = 10 ⁻³ wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ wanted signal at -72 dBm, modulate	Data rate error tolerance		> (- 125 / 100)	ppm
at ±1 MHz, BER = 10 -3 Selectivity, ±2 MHz ⁽¹⁾ Wanted signal at -79 dBm, modulated interferer at ±2 MHz, BER = 10 -3 Wanted signal at -79 dBm, modulated interferer at ±3 MHz, BER = 10 -3 Selectivity, ±4 MHz ⁽¹⁾ Wanted signal at -79 dBm, modulated interferer at ±3 MHz, BER = 10 -3 Selectivity, ±4 MHz ⁽¹⁾ Wanted signal at -79 dBm, modulated interferer at ±4 MHz, BER = 10 -3 Selectivity, ±6 MHz ⁽¹⁾ Wanted signal at -79 dBm, modulated interferer at ≥ ±6 MHz, BER = 10 -3 Selectivity, ±7 MHz Wanted signal at -79 dBm, modulated interferer at ≥ ±7 MHz, BER = 10 -3 Selectivity, Image frequency ⁽¹⁾ Selectivity, Image frequency ⁽¹⁾ Note that Image frequency ±10 Note that Image frequency ±10 Note that Image frequency ±10 MHz ⁽¹⁾ Note that Image frequency ±11 MHz is the Co-channel -1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz, Wanted signal at ±1 MHz from image frequency, BER = 10 -3 Solok kips (LE Coded) Receiver sensitivity Differential mode. BER = 10 -3 Difference between the incoming carrier frequency and the internally generated data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 -3 Selectivity, ±2 MHz ⁽¹⁾ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 -3 Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 -3 Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 -3	Co-channel rejection ⁽¹⁾		- 1.5	dB
at ±2 MHz, BER = 10 - 3 Selectivity, ±3 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±3 MHz, BER = 10 - 3 Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Selectivity, ±7 MHz Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Wanted signal at - 79 dBm, modulated interferer at ± ±7 MHz, BER = 10 - 3 Selectivity, Image frequency ⁽¹⁾ Wanted signal at - 79 dBm, modulated interferer at image frequency, BER = 10 - 3 Note that Image frequency ±1 MHz is the Cochannel - 1 MHz. Wanted signal at - 79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 - 3 Selectivity, Image frequency, BER = 10 - 3 Note that Image frequency ±1 MHz from image frequency, BER = 10 - 3 Selectiver sensitivity Differential mode. BER = 10 - 3 Differential mode. BER = 10 - 3 >5 dBi Difference between the incoming carrier frequency and the internally generated carrier frequency and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at - 72 dBm, modulated interferer at ±1 MHz BER = 10 - 3 Selectivity, ±1 MHz ⁽¹⁾ Wanted signal at - 72 dBm, modulated interferer at ±1 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±1 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3	Selectivity, ±1 MHz ⁽¹⁾	Wanted signal at -79 dBm, modulated interferer at ± 1 MHz, BER = 10^{-3}	8 / 4.5 ⁽²⁾	dB
at ±3 MHz, BER = 10 - 3 Selectivity, ±4 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Wanted signal at - 79 dBm, modulated interferer at ±4 MHz, BER = 10 - 3 Wanted signal at - 79 dBm, modulated interferer at ≥ ±6 MHz, BER = 10 - 3 Selectivity, ±6 MHz(1) Wanted signal at - 79 dBm, modulated interferer at ≥ ±7 MHz, BER = 10 - 3 Selectivity, Image frequency(1) Wanted signal at - 79 dBm, modulated interferer at ≥ ±7 MHz, BER = 10 - 3 Selectivity, Image frequency(1) Wanted signal at - 79 dBm, modulated interferer at image frequency, BER = 10 - 3 Note that Image frequency +1 MHz is the Co-channel -1 MHz. Wanted signal at - 79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 - 3 Solectivity, Image frequency +1 MHz is the Co-channel -1 MHz. Wanted signal at - 79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 - 3 Solok kbps (LE Coded) Receiver sensitivity Differential mode. BER = 10 - 3 Differential mode. BER = 10 - 3 > 50 dBi Selectivity, ±1 MHz(1) Difference between the incoming carrier frequency and the internally generated data rate and the internally generated data rate (37-byte packets) Difference between incoming data rate and the internally generated data rate (37-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at - 72 dBm, modulated interferer at ±1 MHz, BER = 10 - 3 Selectivity, ±1 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±1 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±1 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm, modulated interferer at ±2 MHz, BER = 10 - 3 Wanted signal at - 72 dBm,	Selectivity, ±2 MHz ⁽¹⁾	Wanted signal at -79 dBm, modulated interferer at ± 2 MHz, BER = 10^{-3}	44 / 37 ⁽²⁾	dB
at ±4 MHz, BER = 10 ⁻³ Selectivity, ±6 MHz ⁽¹⁾ Wanted signal at −79 dBm, modulated interferer at ≥ ±6 MHz, BER = 10 ⁻³ Wanted signal at −79 dBm, modulated interferer at ≥ ±7 MHz, BER = 10 ⁻³ Selectivity, ±7 MHz Wanted signal at −79 dBm, modulated interferer at ≥ ±7 MHz, BER = 10 ⁻³ Wanted signal at −79 dBm, modulated interferer at image frequency. BER = 10 ⁻³ Wanted signal at −79 dBm, modulated interferer at image frequency. BER = 10 ⁻³ Note that Image frequency ±1 the Co-channel −1 MHz. Wanted signal at −79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³ Note that Image frequency ±1 MHz from image frequency +1 MHz from image frequency, BER = 10 ⁻³ Note that Image frequency = 10 MHz. Wanted signal at −79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³ Note that Image frequency = 10 MHz from image frequency = 10 MHz. Wanted signal at −79 dBm, modulated interferer at ±10 MHz from image frequency and the internal mode. BER = 10 ⁻³ Prequency error tolerance Difference between the incoming carrier frequency and the internally generated carrier frequency and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at −72 dBm, modulated interferer at ±1 MHz fill MHz fill Manted signal at −72 dBm, modulated interferer at ±1 MHz fill Manted signal at −72 dBm, modulated interferer at ±2 MHz fill MHz fill Manted signal at −72 dBm, modulated interferer at ±2 MHz fill Manted signal at −72 dBm, modulated interferer at ±2 MHz fill Manted signal at −72 dBm, modulated interferer at ±2 MHz fill Manted signal at −72 dBm, modulated interferer at ±2 MHz fill Manted signal at −72 dBm, modulated interferer at ±2 MHz fill Manted signal at −72 dBm, modulated interferer at ±2 MHz fill	Selectivity, ±3 MHz ⁽¹⁾		46 / 44 ⁽²⁾	dB
at ≥ ±6 MHz, BER = 10 − 3 Selectivity, ±7 MHz Wanted signal at −79 dBm, modulated interferer at ≥ ±7 MHz, BER = 10 − 3 Wanted signal at −79 dBm, modulated interferer at ± mage frequency. Wanted signal at −79 dBm, modulated interferer at ± mage frequency. BER = 10 − 3 Note that Image frequency ±1 MHz is the Co-channel −1 MHz. Wanted signal at −79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 − 3 Solectivity, Image frequency ±1 MHz(1) Differential mode. BER = 10 − 3 Frequency error tolerance Difference between the incoming carrier frequency and the internally generated carrier frequency and the internally generated carrier frequency between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at −72 dBm, modulated interferer in channel, BER = 10 − 3 Selectivity, ±1 MHz(1) Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz (1) Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz (1) Wanted signal at −72 dBm, modulated interferer at ±1 MHz, BER = 10 − 3 Wanted signal at −72 dBm, modulated interferer at ±1 MHz (1) Wanted signal	Selectivity, ±4 MHz ⁽¹⁾		44 / 46 ⁽²⁾	dB
at ≥ ±7 MHz, BER = 10 ⁻³ Selectivity, Image frequency(1) Wanted signal at -79 dBm, modulated interferer at image frequency, BER = 10 ⁻³ Note that Image frequency +1 MHz is the Cochannel -1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³ Solectivity, Image frequency ±1 Note that Image frequency +1 MHz is the Cochannel -1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³ Solectivity Differential mode. BER = 10 ⁻³ Differential mode. BER = 10 ⁻³ Difference between the incoming carrier frequency and the internally generated carrier frequency Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Selectivity, ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³	Selectivity, ±6 MHz ⁽¹⁾		48 / 44 ⁽²⁾	dB
at image frequency, BER = 10 ⁻³ Note that Image frequency + 1 MHz is the Co- channel - 1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³ Note that Image frequency + 1 MHz is the Co- channel - 1 MHz. Wanted signal at -79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³ Differential mode. BER = 10 ⁻³ Prequency saturation Differential mode. BER = 10 ⁻³ Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³	Selectivity, ±7 MHz	,	51 / 45 ⁽²⁾	dB
Selectivity, Image frequency ±1 modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³ 500 kbps (LE Coded) Receiver sensitivity Differential mode. BER = 10 ⁻³ -100 dBi Receiver saturation Differential mode. BER = 10 ⁻³ >5 dBi Differential mode. BER = 10 ⁻³ >5 dBi Differential mode. BER = 10 ⁻³ >5 dBi Difference between the incoming carrier frequency and the internally generated carrier frequency and the internally generated data rate and the internally generated data rate (37-byte packets) > (-450 / 450) pproperties of the packets > (-150 / 175)	Selectivity, Image frequency ⁽¹⁾		37	dB
Receiver sensitivity Differential mode. BER = 10 ⁻³ Prequency activity. 1 Differential mode. BER = 10 ⁻³ Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³		channel - 1 MHz. Wanted signal at - 79 dBm, modulated interferer at ±1 MHz from image	4.5 / 44 ⁽²⁾	dB
Receiver saturation Differential mode. BER = 10 ⁻³ Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³	500 kbps (LE Coded)			
Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1)	Receiver sensitivity	Differential mode. BER = 10 ⁻³	- 100	dBm
frequency error tolerance frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at - 72 dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at - 72 dBm, modulated interferer at ±2 MHz(1	Receiver saturation	Differential mode. BER = 10 ⁻³	> 5	dBm
internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at -72 dBm, modulated interferer in channel, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³ Selectivity, ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³ Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ±2 MHz(1)	Frequency error tolerance	frequency and the internally generated carrier	> (- 300 / 300)	kHz
internally generated data rate (255-byte packets) $> (-150/175)$ ppi internally generated data rate (255-byte packets) $> (-150/175)$ ppi internally generated data rate (255-byte packets) $> (-150/175)$ dE Co-channel rejection(1) Wanted signal at -72 dBm, modulated interferer at ± 1 MHz(1) Wanted signal at -72 dBm, modulated interferer at ± 1 MHz(1) Wanted signal at -72 dBm, modulated interferer at ± 2 MHz(1) Wanted signal at -72 dBm, modulated interferer wanted wa	Data rate error tolerance	j –	> (- 450 / 450)	ppm
Selectivity, $\pm 1 \text{ MHz}^{(1)}$ Wanted signal at -72 dBm , modulated interferer at $\pm 1 \text{ MHz}^{(1)}$ Wanted signal at -72 dBm , modulated interferer at $\pm 1 \text{ MHz}^{(1)}$ Wanted signal at -72 dBm , modulated interferer at $\pm 2 \text{ MHz}^{(1)}$ Wanted signal at -72 dBm , modulated interferer at $\pm 2 \text{ MHz}^{(1)}$ Wanted signal at -72 dBm , modulated interferer 43 / 35 (2) Wanted signal at -72 dBm , modulated interferer 46 / 46(2)	Data rate error tolerance	j –	> (- 150 / 175)	ppm
at ± 1 MHz, BER = 10^{-3} Wanted signal at -72 dBm, modulated interferer at ± 2 MHz(1) Wanted signal at -72 dBm, modulated interferer at ± 2 MHz(1) Wanted signal at -72 dBm, modulated interferer Wanted signal at -72 dBm, modulated interferer	Co-channel rejection ⁽¹⁾		- 3.5	dB
at ± 2 MHz, BER = 10^{-3} Wanted signal at -72 dBm, modulated interferer 43 / 35 (-) 45 / 46(2)	Selectivity, ±1 MHz ⁽¹⁾		8 / 4 ⁽²⁾	dB
	Selectivity, ±2 MHz ⁽¹⁾		43 / 35 ⁽²⁾	dB
	Selectivity, ±3 MHz ⁽¹⁾		46 / 46 ⁽²⁾	dB

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8.10 Bluetooth Low Energy - Receive (RX) (continued)

When measured on the CC26x2REM-7ID reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Selectivity, ±4 MHz ⁽¹⁾	Wanted signal at - 72 dBm, modulated interferer at ±4 MHz, BER = 10 ⁻³	45 / 47 ⁽²⁾		dB
Selectivity, ±6 MHz ⁽¹⁾	Wanted signal at -72 dBm, modulated interferer at \geq ±6 MHz, BER = 10 $^{-3}$	46 / 45 ⁽²⁾		dB
Selectivity, ±7 MHz	Wanted signal at -72 dBm, modulated interferer at \geq ±7 MHz, BER = 10 $^{-3}$	49 / 45 ⁽²⁾		dB
Selectivity, Image frequency ⁽¹⁾	Wanted signal at - 72 dBm, modulated interferer at image frequency, BER = 10 ⁻³	35		dB
Selectivity, Image frequency ±1 MHz ⁽¹⁾	Note that Image frequency + 1 MHz is the Co- channel - 1 MHz. Wanted signal at - 72 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³	4 / 46 ⁽²⁾		dB
1 Mbps (LE 1M)				
Receiver sensitivity	Differential mode. BER = 10 ⁻³	- 97		dBm
Receiver saturation	Differential mode. BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (- 350 / 350)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (- 650 / 750)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer in channel, BER = 10 ⁻³	- 6		dB
Selectivity, ±1 MHz ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer at ±1 MHz, BER = 10 - 3	7 / 4 ⁽²⁾		dB
Selectivity, ±2 MHz ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer at ±2 MHz,BER = 10 - 3	39 / 33 ⁽²⁾		dB
Selectivity, ±3 MHz ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer at ±3 MHz, BER = 10 ⁻³	36 / 40 (2)		dB
Selectivity, ±4 MHz ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer at ±4 MHz, BER = 10 - 3	36 / 45 ⁽²⁾		dB
Selectivity, ±5 MHz or more ⁽¹⁾	Wanted signal at − 67 dBm, modulated interferer at ≥ ±5 MHz, BER = 10 ⁻³	40		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer at image frequency, BER = 10 ⁻³	33		dB
Selectivity, image frequency ±1 MHz ⁽¹⁾	Note that Image frequency + 1 MHz is the Co- channel - 1 MHz. Wanted signal at - 67 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³	4 / 41 ⁽²⁾		dB
Out-of-band blocking ⁽³⁾	30 MHz to 2000 MHz	- 10		dBm
Out-of-band blocking	2003 MHz to 2399 MHz	- 18		dBm
Out-of-band blocking	2484 MHz to 2997 MHz	- 12		dBm
Out-of-band blocking	3000 MHz to 12.75 GHz	- 2		dBm
Intermodulation	Wanted signal at 2402 MHz, - 64 dBm. Two interferers at 2405 and 2408 MHz respectively, at the given power level	- 42		dBm
Spurious emissions, 30 to 1000 MHz ⁽⁴⁾	Measurement in a 50- Ω single-ended load.	< - 59		dBm

8.10 Bluetooth Low Energy - Receive (RX) (continued)

When measured on the CC26x2REM-7ID reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Spurious emissions, 1 to 12.75 GHz ⁽⁴⁾	Measurement in a 50- Ω single-ended load.	< -47		dBm
RSSI dynamic range		70		dB
RSSI accuracy		±4		dB
2 Mbps (LE 2M)				
Receiver sensitivity	Differential mode. Measured at SMA connector, BER = 10 ⁻³	- 91		dBm
Receiver saturation	Differential mode. Measured at SMA connector, BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (- 500 / 500)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (- 700 / 750)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at $^-$ 67 dBm, modulated interferer in channel,BER = 10^{-3}	- 7		dB
Selectivity, ±2 MHz ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer at ±2 MHz, Image frequency is at - 2 MHz, BER = 10^{-3}	8 / 4 ⁽²⁾		dB
Selectivity, ±4 MHz ⁽¹⁾	Wanted signal at -67 dBm, modulated interferer at ± 4 MHz, BER = 10^{-3}	36 / 34 ⁽²⁾		dB
Selectivity, ±6 MHz ⁽¹⁾	Wanted signal at -67 dBm, modulated interferer at ± 6 MHz, BER = 10^{-3}	37 / 36 ⁽²⁾		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at - 67 dBm, modulated interferer at image frequency, BER = 10 ⁻³	4		dB
Selectivity, image frequency ±2 MHz ⁽¹⁾	Note that Image frequency + 2 MHz is the Cochannel. Wanted signal at $^-$ 67 dBm, modulated interferer at ± 2 MHz from image frequency, BER = 10^{-3}	- 7 / 36 ⁽²⁾		dB
Out-of-band blocking ⁽³⁾	30 MHz to 2000 MHz	- 16		dBm
Out-of-band blocking	2003 MHz to 2399 MHz	- 21		dBm
Out-of-band blocking	2484 MHz to 2997 MHz	- 15		dBm
Out-of-band blocking	3000 MHz to 12.75 GHz	- 12		dBm
Intermodulation	Wanted signal at 2402 MHz, - 64 dBm. Two interferers at 2408 and 2414 MHz respectively, at the given power level	- 38		dBm

⁽¹⁾ Numbers given as I/C dB

⁽²⁾ X / Y, where X is +N MHz and Y is - N MHz

⁽³⁾ Excluding one exception at F_{wanted} / 2, per Bluetooth Specification

⁽⁴⁾ Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan)



8.11 Bluetooth Low Energy - Transmit (TX)

When measured on the CC26x2REM-7ID reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	Т	EST CONDITIONS	MIN	TYP MA	X UNIT
General Parameters	S				
Max output power	Differential mode, delivered to a	single-ended 50 Ω load through a balun		5	dBm
Output power programmable range	Differential mode, delivered to a single-ended 50 Ω load through a balun			26	dB
Spurious emissions	s and harmonics				
	f < 1 GHz, outside restricted bands	+5 dBm setting	<	- 36	dBm
Spurious emissions	f < 1 GHz, restricted bands ETSI		<	- 54	dBm
	f < 1 GHz, restricted bands FCC		<	- 55	dBm
	f > 1 GHz, including harmonics		<	- 42	dBm
Harmonics (1)	Second harmonic		<	- 42	dBm
	Third harmonic		<	- 42	dBm

⁽¹⁾ Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).

8.12 Timing and Switching Characteristics

8.12.1 Reset Timing

PARAMETER	MIN	TYP	MAX	UNIT
RESET_N low duration	1			μs

8.12.2 Wakeup Timing

Measured over operating free-air temperature with V_{DDS} = 3.0 V (unless otherwise noted). The times listed here do not include software overhead.

include contract eventuals.						
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
MCU, Reset to Active ⁽¹⁾		85	0 - 3000		μs	
MCU, Shutdown to Active ⁽¹⁾		85	0 - 3000		μs	
MCU, Standby to Active			160		μs	
MCU, Active to Standby			36		μs	
MCU, Idle to Active			14		μs	

⁽¹⁾ The wakeup time is dependent on remaining charge on VDDR capacitor when starting the device, and thus how long the device has been in Reset or Shutdown before starting up again. The wake up time increases with a higher capacitor value.

Product Folder Links: CC2642R

8.12.3 Clock Specifications

8.12.3.1 48 MHz Crystal Oscillator (XOSC_HF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted. (1)

	PARAMETER	MIN	TYP	MAX	UNIT
	Crystal frequency		48		MHz
ESR	Equivalent series resistance $ 6 \text{ pF} < C_L \leqslant 9 \text{ pF} $		20	60	Ω
ESR	Equivalent series resistance $5 \text{ pF} < C_L \leqslant 6 \text{ pF}$			80	Ω
L _M	Motional inductance, relates to the load capacitance that is used for the crystal (C _L in Farads) ⁽⁵⁾		$< 3 \times 10^{-25} / C_L^2$		Н
C _L	Crystal load capacitance ⁽⁴⁾	5	7 ⁽³⁾	9	pF
	Start-up time ⁽²⁾		200		μs

- (1) Probing or otherwise stopping the crystal while the DC/DC converter is enabled may cause permanent damage to the device.
- Start-up time using the TI-provided power driver. Start-up time may increase if driver is not used.
- (3) On-chip default connected capacitance including reference design parasitic capacitance. Connected internal capacitance is changed through software in the Customer Configuration section (CCFG).
- (4) Adjustable load capacitance is integrated into the device.
- (5) The crystal manufacturer's specification must satisfy this requirement for proper operation.

8.12.3.2 48 MHz RC Oscillator (RCOSC_HF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Frequency		48		MHz
Uncalibrated frequency accuracy		±1		%
Calibrated frequency accuracy ⁽¹⁾		±0.25		%
Start-up time		5		μs

⁽¹⁾ Accuracy relative to the calibration source (XOSC_HF)

8.12.3.3 2 MHz RC Oscillator (RCOSC_MF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Calibrated frequency		2		MHz
Start-up time		5		μs

8.12.3.4 32.768 kHz Crystal Oscillator (XOSC LF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

		MIN	TYP	MAX	UNIT
	Crystal frequency		32.768		kHz
ESR	Equivalent series resistance		30	100	kΩ
C_L	Crystal load capacitance	6	7 ⁽¹⁾	12	pF

Default load capacitance using TI reference designs including parasitic capacitance. Crystals with different load capacitance may be used.

8.12.3.5 32 kHz RC Oscillator (RCOSC LF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

	,			
	MIN	TYP	MAX	UNIT
Calibrated frequency		32.8 ⁽¹⁾		kHz

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8.12.3.5 32 kHz RC Oscillator (RCOSC_LF) (continued)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Temperature coefficient.		50		ppm/°C

(1) When using RCOSC_LF as source for the low frequency system clock (SCLK_LF), the accuracy of the SCLK_LF-derived Real Time Clock (RTC) can be improved by measuring RCOSC_LF relative to XOSC_HF and compensating for the RTC tick speed. This functionality is available through the TI-provided Power driver.

Product Folder Links: CC2642R

8.12.4 Synchronous Serial Interface (SSI) Characteristics

8.12.4.1 Synchronous Serial Interface (SSI) Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER NO.		PARAMETER	MIN	TYP	MAX	UNIT
S1	t _{clk_per}	SSICIk cycle time	12		65024	System Clocks (2)
S2 ⁽¹⁾	t _{clk_high}	SSICIk high time		0.5		t _{clk_per}
S3 ⁽¹⁾	t _{clk_low}	SSICIk low time		0.5		t _{clk_per}

- (1) Refer to SSI timing diagrams 图 8-1, 图 8-2, and 图 8-3
- (2) When using the TI-provided Power driver, the SSI system clock is always 48 MHz.

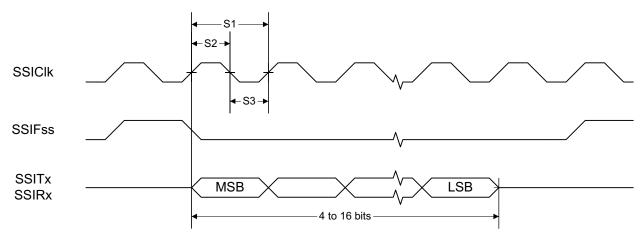


图 8-1. SSI Timing for TI Frame Format (FRF = 01), Single Transfer Timing Measurement

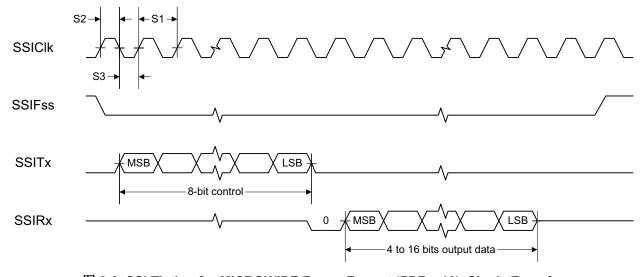
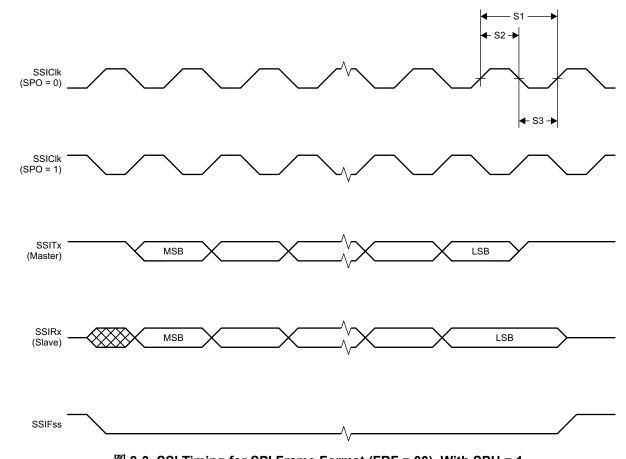


图 8-2. SSI Timing for MICROWIRE Frame Format (FRF = 10), Single Transfer





 \boxtimes 8-3. SSI Timing for SPI Frame Format (FRF = 00), With SPH = 1

8.12.5 UART

8.12.5.1 UART Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	MIN	TYP	MAX	UNIT
UART rate			3	MBaud

8.13 Peripheral Characteristics

8.13.1 ADC

8.13.1.1 Analog-to-Digital Converter (ADC) Characteristics

 T_c = 25 °C, V_{DDS} = 3.0 V and voltage scaling enabled, unless otherwise noted.⁽¹⁾ Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Input voltage range		0		VDDS	V
	Resolution			12		Bits
	Sample Rate				200	ksps
	Offset	Internal 4.3 V equivalent reference ⁽²⁾		- 0.24		LSB
	Gain error	Internal 4.3 V equivalent reference ⁽²⁾		7.14		LSB
DNL ⁽⁴⁾	Differential nonlinearity			> - 1		LSB
INL	Integral nonlinearity			±4		LSB
		Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone		9.8		
		Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone, DC/DC enabled		9.8		
		VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		10.1		
ENOB	Effective number of bits	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		11.1		Bits
		Internal reference, voltage scaling disabled, 14-bit mode, 200 kSamples/s, 600 Hz input tone ⁽⁵⁾		11.3		
		Internal reference, voltage scaling disabled, 15-bit mode, 200 kSamples/s, 150 Hz input tone ⁽⁵⁾		11.6		
		Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone		- 65		
THD	Total harmonic distortion	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		- 70		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		- 72		
		Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone		60		
SINAD, SNDR	Signal-to-noise and	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		63		dB
	distortion ratio	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		68		
		Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone		70		
SFDR	Spurious-free dynamic range	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		73		dB
	9	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		75		
	Conversion time	Serial conversion, time-to-output, 24 MHz clock		50		Clock Cycles
	Current consumption	Internal 4.3 V equivalent reference ⁽²⁾		0.42		mA
	Current consumption	VDDS as reference		0.6		mA



8.13.1.1 Analog-to-Digital Converter (ADC) Characteristics (continued)

 T_c = 25 °C, V_{DDS} = 3.0 V and voltage scaling enabled, unless otherwise noted.⁽¹⁾

Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reference voltage	Equivalent fixed internal reference (input voltage scaling enabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/offset compensation factors stored in FCFG1	4	1.3 ⁽²⁾ (3)		V
Reference voltage	Fixed internal reference (input voltage scaling disabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/offset compensation factors stored in FCFG1. This value is derived from the scaled value (4.3 V) as follows: V _{ref} = 4.3 V × 1408 / 4095		1.48		V
Reference voltage	VDDS as reference, input voltage scaling enabled		VDDS		V
Reference voltage	VDDS as reference, input voltage scaling disabled	\	/DDS / 2.82 ⁽³⁾		V
Input impedance	200 kSamples/s, voltage scaling enabled. Capacitive input, Input impedance depends on sampling frequency and sampling time		>1		МΩ

- (1) Using IEEE Std 1241-2010 for terminology and test methods
- (2) Input signal scaled down internally before conversion, as if voltage range was 0 to 4.3 V
- (3) Applied voltage must be within Absolute Maximum Ratings (see 节 8.1) at all times
- (4) No missing codes
- (5) ADC output = Σ (4ⁿ samples) >> n, n = desired extra bits

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8.13.2 DAC

8.13.2.1 Digital-to-Analog Converter (DAC) Characteristics

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	FARAMETER PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
enera	al Parameters					
	Resolution			8		Bits
		Any load, any V _{REF} , pre-charge OFF, DAC charge-pump ON	1.8		3.8	
$V_{ m DDS}$	Supply voltage	External Load ⁽⁴⁾ , any V _{REF} , pre-charge OFF, DAC charge-pump OFF	2.0		3.8	V
		Any load, V _{REF} = DCOUPL, pre-charge ON	2.6		3.8	
	0, 1, 6	Buffer ON (recommended for external load)	16		250	
DAC	Clock frequency	Buffer OFF (internal load)	16		1000	kHz
	V-16	V _{REF} = VDDS, buffer OFF, internal load		13		
	Voltage output settling time	V _{REF} = VDDS, buffer ON, external capacitive load = 20 pF ⁽³⁾		13.8		1 / F _{DAC}
	External capacitive load			20	200	pF
	External resistive load		10			ΜΩ
	Short circuit current				400	μA
		VDDS = 3.8 V, DAC charge-pump OFF		50.8		
	Max output impedance Vref = VDDS, buffer ON, CLK 250 kHz	VDDS = 3.0 V, DAC charge-pump ON		51.7		
		VDDS = 3.0 V, DAC charge-pump OFF		53.2		
MAX		VDDS = 2.0 V, DAC charge-pump ON		48.7		$\mathbf{k} \Omega$
		VDDS = 2.0 V, DAC charge-pump OFF		70.2		
		VDDS = 1.8 V, DAC charge-pump ON		46.3		
		VDDS = 1.8 V, DAC charge-pump OFF		88.9		
nterna	Load - Continuous Time	Comparator / Low Power Clocked Comparator				
NA.II	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 250 kHz		±1		
ONL	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 16 kHz		±1.2		LSB ⁽¹⁾
		V _{REF} = VDDS = 3.8 V		±0.64		
		V _{REF} = VDDS= 3.0 V		±0.81		
	Offset error ⁽²⁾ Load = Continuous Time	V _{REF} = VDDS = 1.8 V		±1.27		LSB ⁽¹⁾
	Comparator	V _{REF} = DCOUPL, pre-charge ON		±3.43		LOD
		V _{REF} = DCOUPL, pre-charge OFF		±2.88		
		V _{REF} = ADCREF		±2.37		
		V _{REF} = VDDS= 3.8 V		±0.78		
		V _{REF} = VDDS = 3.0 V		±0.77		
	Offset error ⁽²⁾ Load = Low Power	V _{REF} = VDDS= 1.8 V		±3.46		LSB ⁽¹⁾
	Clocked Comparator	V _{REF} = DCOUPL, pre-charge ON		±3.44		LOD
		V _{REF} = DCOUPL, pre-charge OFF		±4.70		
		V _{REF} = ADCREF		±4.11		



8.13.2.1 Digital-to-Analog Converter (DAC) Characteristics (continued)

T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
		V _{REF} = VDDS = 3.8 V	±1.53		
	Max code output voltage	V _{REF} = VDDS = 3.0 V	±1.71		
	variation ⁽²⁾	V _{REF} = VDDS= 1.8 V	±2.10		LSB ⁽¹⁾
	Load = Continuous Time	V _{REF} = DCOUPL, pre-charge ON	±6.00		LSB(*)
	Comparator	V _{REF} = DCOUPL, pre-charge OFF	±3.85		
		V _{REF} = ADCREF	±5.84		
		V _{REF} = VDDS= 3.8 V	±2.92		
	Mary and a system of college	V _{REF} =VDDS= 3.0 V	±3.06		
	Max code output voltage variation ⁽²⁾	V _{REF} = VDDS= 1.8 V	±3.91		L OD(1)
	Load = Low Power	V _{REF} = DCOUPL, pre-charge ON	±7.84		LSB ⁽¹⁾
	Clocked Comparator	V _{REF} = DCOUPL, pre-charge OFF	±4.06		
		V _{REF} = ADCREF	±6.94		
		V _{REF} = VDDS = 3.8 V, code 1	0.03		
		V _{REF} = VDDS = 3.8 V, code 255	3.62		
		V _{REF} = VDDS= 3.0 V, code 1	0.02		
		V _{REF} = VDDS= 3.0 V, code 255	2.86		
		V _{REF} = VDDS= 1.8 V, code 1	0.01		
	Output voltage range ⁽²⁾	V _{REF} = VDDS = 1.8 V, code 255	1.71		
	Load = Continuous Time Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.01		V
		V _{REF} = DCOUPL, pre-charge OFF, code 255	1.21		
		V _{REF} = DCOUPL, pre-charge ON, code 1	1.27		
		V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
		V _{REF} = ADCREF, code 1	0.01		
		V _{REF} = ADCREF, code 255	1.41		
		V _{REF} = VDDS = 3.8 V, code 1	0.03		
		V _{REF} = VDDS= 3.8 V, code 255	3.61		
		V _{RFF} = VDDS= 3.0 V, code 1	0.02		
		V _{RFF} = VDDS= 3.0 V, code 255	2.85		
		V _{REF} = VDDS = 1.8 V, code 1	0.01		
	Output voltage range ⁽²⁾	V _{REF} = VDDS = 1.8 V, code 255	1.71		
	Load = Low Power Clocked Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.01		V
	Glooked Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 255	1.21		
		V _{RFF} = DCOUPL, pre-charge ON, code 1	1.27		
		V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
		V _{REF} = ADCREF, code 1	0.01		
		V _{REF} = ADCREF, code 255	1.41		
ern	al Load (Keysight 34401A	_ · · - ·	I		
	, , , ,	V _{REF} = VDDS, F _{DAC} = 250 kHz	±1		
	Integral nonlinearity	V _{REF} = DCOUPL, F _{DAC} = 250 kHz	±1		LSB ⁽¹⁾
]	V _{REF} = ADCREF, F _{DAC} = 250 kHz	±1		
IL	Differential nonlinearity	V _{REF} = VDDS, F _{DAC} = 250 kHz	±1		LSB ⁽¹⁾

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8.13.2.1 Digital-to-Analog Converter (DAC) Characteristics (continued)

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Offset error	V _{REF} = VDDS= 3.8 V	±0.40		
	V _{REF} = VDDS= 3.0 V	±0.50		
	V _{REF} = VDDS = 1.8 V	±0.75		LSB ⁽¹⁾
	V _{REF} = DCOUPL, pre-charge ON	±1.55		LOD(1)
	V _{REF} = DCOUPL, pre-charge OFF	±1.30		
	V _{REF} = ADCREF	±1.10		
	V _{REF} = VDDS= 3.8 V	±1.00		
	V _{REF} = VDDS= 3.0 V	±1.00		
Max code output voltage	V _{REF} = VDDS= 1.8 V	±1.00		LSB ⁽¹⁾
variation	V _{REF} = DCOUPL, pre-charge ON	±3.45		LSB(··)
	V _{REF} = DCOUPL, pre-charge OFF	±2.10		
	V _{REF} = ADCREF	±1.90		
	V _{REF} = VDDS = 3.8 V, code 1	0.03		
	V _{REF} = VDDS = 3.8 V, code 255	3.61		
	V _{REF} = VDDS = 3.0 V, code 1	0.02		
	V _{REF} = VDDS= 3.0 V, code 255	2.85		
	V _{REF} = VDDS= 1.8 V, code 1	0.02		
Output voltage range Load = Low Power	V _{REF} = VDDS = 1.8 V, code 255	1.71		V
Clocked Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.02		V
•	V _{REF} = DCOUPL, pre-charge OFF, code 255	1.20		
	V _{REF} = DCOUPL, pre-charge ON, code 1	1.27		
	V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
	V _{REF} = ADCREF, code 1	0.02		
	V _{REF} = ADCREF, code 255	1.42		

^{(1) 1} LSB (V_{REF} 3.8 V/3.0 V/1.8 V/DCOUPL/ADCREF) = 14.10 mV/11.13 mV/6.68 mV/4.67 mV/5.48 mV (2) Includes comparator offset

⁽³⁾ A load > 20 pF will increases the settling time

Keysight 34401A Multimeter



8.13.3 Temperature and Battery Monitor

8.13.3.1 Temperature Sensor

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			2		°C
Accuracy	-40 °C to 0 °C		±4.0		°C
Accuracy	0 °C to 105 °C		±2.5		°C
Supply voltage coefficient ⁽¹⁾			3.6		°C/V

⁽¹⁾ The temperature sensor is automatically compensated for VDDS variation when using the TI-provided driver.

8.13.3.2 Battery Monitor

Measured on a Texas Instruments reference design with T_c = 25 °C, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			25		mV
Range		1.8		3.8	V
Integral nonlinearity (max)			23		mV
Accuracy	VDDS = 3.0 V		22.5		mV
Offset error			-32		mV
Gain error			-1		%

Product Folder Links: CC2642R

8.13.4 Comparators

8.13.4.1 Low-Power Clocked Comparator

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range		0		V _{DDS}	V
Clock frequency			SCLK_LF		
Internal reference voltage ⁽¹⁾	Using internal DAC with VDDS as reference voltage, DAC code = 0 - 255		0.024 - 2.865		V
Offset	Measured at V _{DDS} / 2, includes error from internal DAC		±5		mV
Decision time	Step from - 50 mV to 50 mV		1		Clock Cycle

⁽¹⁾ The comparator can use an internal 8 bits DAC as its reference. The DAC output voltage range depends on the reference voltage selected. See 节 8.13.2.1

8.13.4.2 Continuous Time Comparator

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range ⁽¹⁾		0		V_{DDS}	V
Offset	Measured at V _{DDS} / 2		±5		mV
Decision time	Step from - 10 mV to 10 mV		0.78		μs
Current consumption	Internal reference		8.6		μA

⁽¹⁾ The input voltages can be generated externally and connected throughout I/Os or an internal reference voltage can be generated using the DAC

8.13.5 Current Source

8.13.5.1 Programmable Current Source

 T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Current source programmable output range (logarithmic range)		0.25 - 20		μА
Resolution		0.25		μA



8.13.6 GPIO

8.13.6.1 GPIO DC Characteristics

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
T _A = 25 °C, V _{DDS} = 1.8 V				
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only	1.56		V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only	0.24		V
GPIO VOH at 4 mA load	IOCURR = 1	1.59		V
GPIO VOL at 4 mA load	IOCURR = 1	0.21		V
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	73		μΑ
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	19		μΑ
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as 0 → 1	1.08		V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as 1 → 0	0.73		٧
GPIO input hysteresis	IH = 1, difference between 0 → 1 and 1 → 0 points	0.35		٧
T _A = 25 °C, V _{DDS} = 3.0 V				
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only	2.59		V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only	0.42		V
GPIO VOH at 4 mA load	IOCURR = 1	2.63		V
GPIO VOL at 4 mA load	IOCURR = 1	0.40		V
T _A = 25 °C, V _{DDS} = 3.8 V				
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	282		μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	110		μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as 0 → 1	1.97		V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as 1 → 0	1.55		٧
GPIO input hysteresis	IH = 1, difference between 0 → 1 and 1 → 0 points	0.42		V
T _A = 25 °C				
VIH	Lowest GPIO input voltage reliably interpreted as a <i>High</i>	0.8*V _{DDS}		V
VIL	Highest GPIO input voltage reliably interpreted as a <i>Low</i>		0.2*V _{DDS}	V

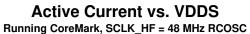
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8.14 Typical Characteristics

All measurements in this section are done with $T_c = 25$ °C and $V_{DDS} = 3.0$ V, unless otherwise noted. See *Recommended Operating Conditions* for device limits. Values exceeding these limits are for reference only.

8.14.1 MCU Current



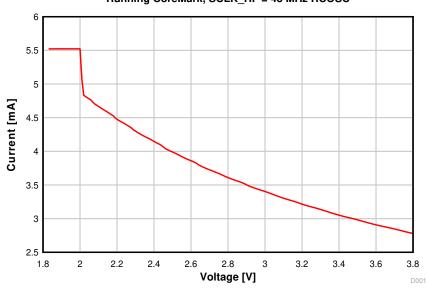


图 8-4. Active Mode (MCU) Current vs. Supply Voltage (VDDS)

Standby Current vs. Temperature

80 kB RAM Retention, no Cache Retention, RTC On SCLK_LF = 32 kHz XOSC

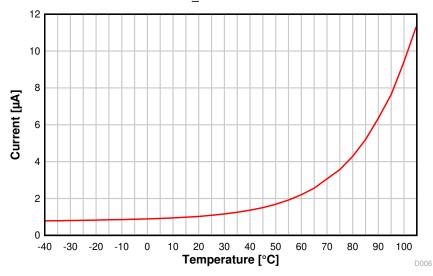


图 8-5. Standby Mode (MCU) Current vs. Temperature

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8.14.2 RX Current

RX Current vs. Temperature BLE 1 Mbps, 2.44 GHz

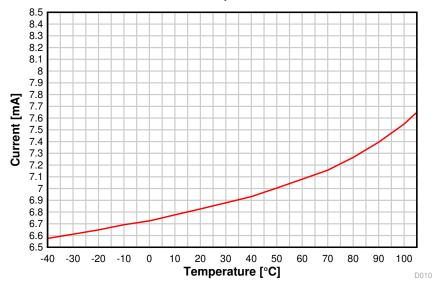


图 8-6. RX Current vs. Temperature (BLE 1 Mbps, 2.44 GHz)

RX Current vs. VDDS

BLE 1 Mbps, 2.44 GHz

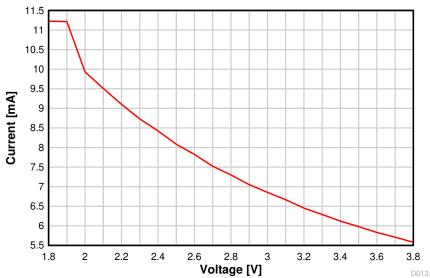


图 8-7. RX Current vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)

8.14.3 TX Current

TX Current vs. Temperature BLE 1 Mbps, 2.44 GHz, 0 dBm

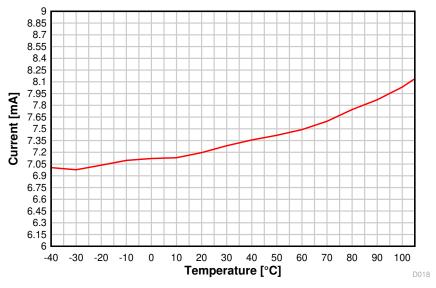


图 8-8. TX Current vs. Temperature (BLE 1 Mbps, 2.44 GHz)

TX Current vs. VDDS

BLE 1 Mbps, 2.44 GHz, 0 dBm

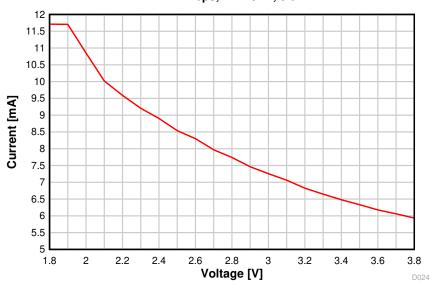


图 8-9. TX Current vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)



表 8-1 shows typical TX current and output power for different output power settings.

表 8-1. Typical TX Current and Output Power

CC2642R at 2.4 GHz, VDDS = 3.0 V (Measured on CC2652REM-7ID)					
txPower	TX Power Setting (SmartRF Studio)	Typical Output Power [dBm]	Typical Current Consumption [mA]		
0x7217	5	4.9	9.5		
0x4E63	4	3.9	9.0		
0x385D	3	2.8	8.6		
0x3259	2	1.8	8.0		
0x2856	1	0.9	7.6		
0x2853	0	-0.3	7.3		
0x12D6	-5	-4.9	6.2		
0x0ACF	-10	-9.4	5.6		
0x06CA	-15	-14.5	5.2		
0x04C6	-20	-20.3	4.8		

8.14.4 RX Performance

Sensitivity vs. Frequency BLE 1 Mbps, 2.44 GHz

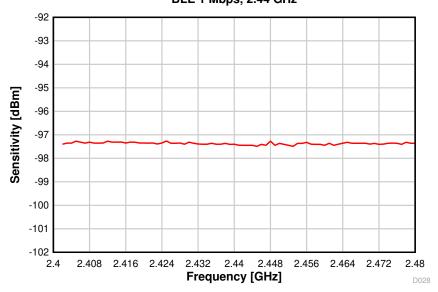


图 8-10. Sensitivity vs. Frequency (BLE 1 Mbps, 2.44 GHz)

Sensitivity vs. Temperature BLE 1 Mbps, 2.44 GHz

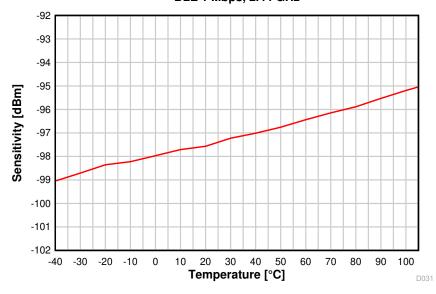


图 8-11. Sensitivity vs. Temperature (BLE 1 Mbps, 2.44 GHz)





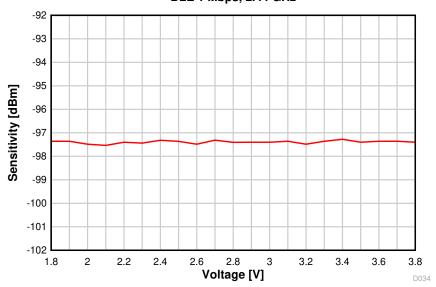


图 8-12. Sensitivity vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)



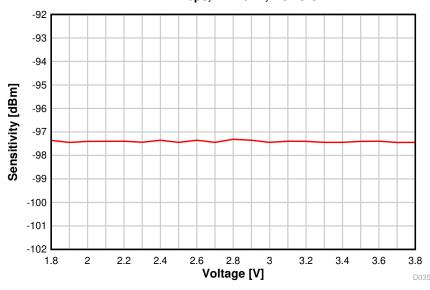


图 8-13. Sensitivity vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz, DCDC Off)

8.14.5 TX Performance

Output Power vs. Temperature BLE 1 Mbps, 2.44 GHz, 0 dBm

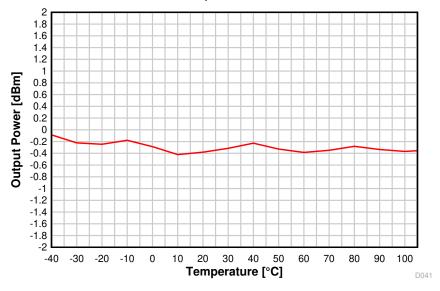


图 8-14. Output Power vs. Temperature (BLE 1 Mbps, 2.44 GHz)

Output Power vs. Temperature

BLE 1 Mbps, 2.44 GHz, +5 dBm

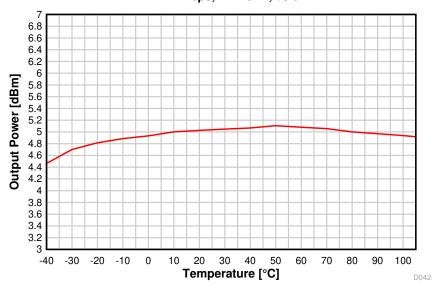


图 8-15. Output Power vs. Temperature (BLE 1 Mbps, 2.44 GHz, +5 dBm)

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Output Power vs. VDDS

BLE 1 Mbps, 2.44 GHz, 0 dBm

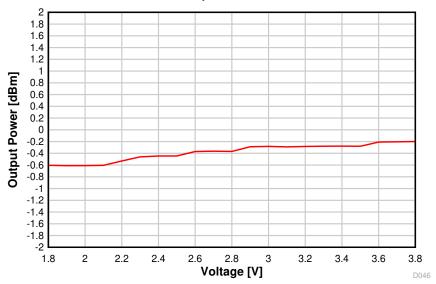


图 8-16. Output Power vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)

Output power vs. VDDS BLE 1 Mbps, 2.44 GHz, +5 dBm

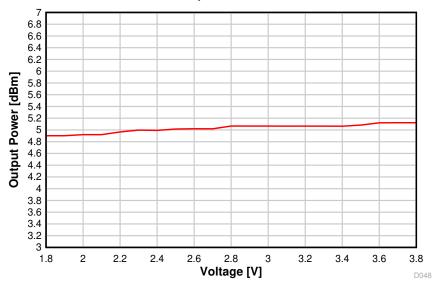


图 8-17. Output Power vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz, +5 dBm)

Output Power vs. Frequency

BLE 1 Mbps, 2.44 GHz, 0 dBm

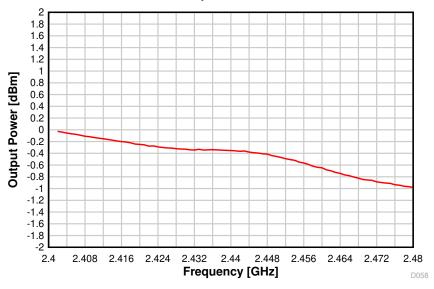


图 8-18. Output Power vs. Frequency (BLE 1 Mbps, 2.44 GHz)

Output Power vs. Frequency

BLE 1 Mbps, 2.44 GHz, +5 dBm

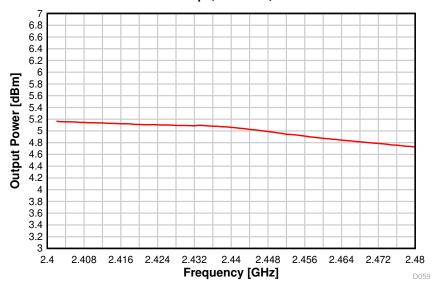


图 8-19. Output Power vs. Frequency (BLE 1 Mbps, 2.44 GHz, +5 dBm)



8.14.6 ADC Performance

ENOB vs. Input Frequency

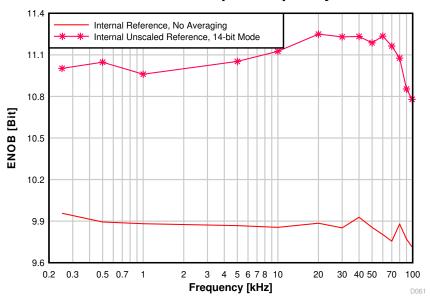


图 8-20. ENOB vs. Input Frequency

ENOB vs. Sampling Frequency

Vin = 3.0 V Sine wave, Internal reference, Fin = Fs / 10

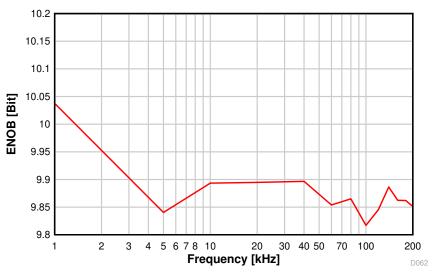


图 8-21. ENOB vs. Sampling Frequency

INL vs. ADC Code

Vin = 3.0 V Sine wave, Internal reference, 200 kSamples/s

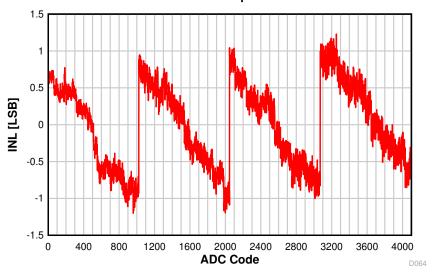


图 8-22. INL vs. ADC Code

DNL vs. ADC Code

Vin = 3.0 V Sine wave, Internal reference, 200 kSamples/s

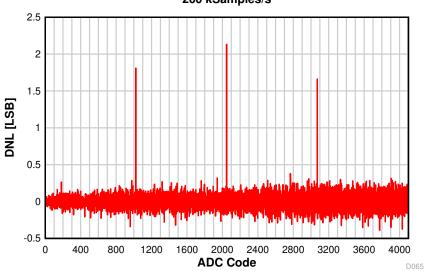


图 8-23. DNL vs. ADC Code



ADC Accuracy vs. Temperature

Vin = 1 V, Internal reference, 200 kSamples/s

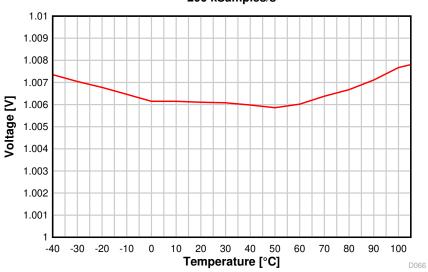


图 8-24. ADC Accuracy vs. Temperature

ADC Accuracy vs. VDDS

Vin = 1 V, Internal reference, 200 kSamples/s

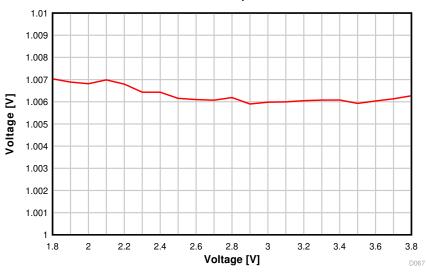


图 8-25. ADC Accuracy vs. Supply Voltage (VDDS)

9 Detailed Description

9.1 Overview

节 4 shows the core modules of the CC2642R device.

9.2 System CPU

The CC2642R SimpleLink[™] Wireless MCU contains an Arm[®] Cortex[®]-M4F system CPU, which runs the application and the higher layers of radio protocol stacks.

The system CPU is the foundation of a high-performance, low-cost platform that meets the system requirements of minimal memory implementation, and low-power consumption, while delivering outstanding computational performance and exceptional system response to interrupts.

Its features include the following:

- ARMv7-M architecture optimized for small-footprint embedded applications
- Arm Thumb®-2 mixed 16- and 32-bit instruction set delivers the high performance expected of a 32-bit Arm core in a compact memory size
- · Fast code execution permits increased sleep mode time
- · Deterministic, high-performance interrupt handling for time-critical applications
- · Single-cycle multiply instruction and hardware divide
- Hardware division and fast digital-signal-processing oriented multiply accumulate
- · Saturating arithmetic for signal processing
- IEEE 754-compliant single-precision Floating Point Unit (FPU)
- · Memory Protection Unit (MPU) for safety-critical applications
- Full debug with data matching for watchpoint generation
 - Data Watchpoint and Trace Unit (DWT)
 - JTAG Debug Access Port (DAP)
 - Flash Patch and Breakpoint Unit (FPB)
- Trace support reduces the number of pins required for debugging and tracing
 - Instrumentation Trace Macrocell Unit (ITM)
 - Trace Port Interface Unit (TPIU) with asynchronous serial wire output (SWO)
- Optimized for single-cycle flash memory access
- Tightly connected to 8-KB 4-way random replacement cache for minimal active power consumption and wait states
- Ultra-low-power consumption with integrated sleep modes
- 48 MHz operation
- 1.25 DMIPS per MHz

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9.3 Radio (RF Core)

The RF Core is a highly flexible and future proof radio module which contains an Arm Cortex-M0 processor that interfaces the analog RF and base-band circuitry, handles data to and from the system CPU side, and assembles the information bits in a given packet structure. The RF core offers a high level, command-based API to the main CPU that configurations and data are passed through. The Arm Cortex-M0 processor is not programmable by customers and is interfaced through the TI-provided RF driver that is included with the SimpleLink Software Development Kit (SDK).

The RF core can autonomously handle the time-critical aspects of the radio protocols, thus offloading the main CPU, which reduces power and leaves more resources for the user application. Several signals are also available to control external circuitry such as RF switches or range extenders autonomously.

A Packet Traffic Arbitrator (PTA) scheme is available for the managed coexistence of BLE and a co-located 2.4-GHz radio. This is based on 802.15.2 recommendations and common industry standards. The 3-wire coexistence interface has multiple modes of operation, encompassing different use cases and number of lines used for signaling. The radio acting as a slave is able to request access to the 2.4-GHz ISM band, and the master to grant it. Information about the request priority and TX or RX operation can also be conveyed.

The various physical layer radio formats are partly built as a software defined radio where the radio behavior is either defined by radio ROM contents or by non-ROM radio formats delivered in form of firmware patches with the SimpleLink SDKs. This allows the radio platform to be updated for support of future versions of standards even with over-the-air (OTA) updates while still using the same silicon.

9.3.1 Bluetooth 5.2 Low Energy

The RF Core offers full support for Bluetooth 5.2 Low Energy, including the high-sped 2-Mbps physical layer and the 500-kbps and 125-kbps long range PHYs (Coded PHY) through the TI provided Bluetooth 5.2 stack or through a high-level Bluetooth API. The Bluetooth 5.2 PHY and part of the controller are in radio and system ROM, providing significant savings in memory usage and more space available for applications.

The new high-speed mode allows data transfers up to 2 Mbps, twice the speed of Bluetooth 4.2 and five times the speed of Bluetooth 4.0, without increasing power consumption. In addition to faster speeds, this mode offers significant improvements for energy efficiency and wireless coexistence with reduced radio communication time.

Bluetooth 5.2 also enables unparalleled flexibility for adjustment of speed and range based on application needs, which capitalizes on the high-speed or long-range modes respectively. Data transfers are now possible at 2 Mbps, enabling development of applications using voice, audio, imaging, and data logging that were not previously an option using Bluetooth low energy. With high-speed mode, existing applications deliver faster responses, richer engagement, and longer battery life. Bluetooth 5.2 enables fast, reliable firmware updates.

9.4 Memory

The up to 352-KB nonvolatile (Flash) memory provides storage for code and data. The flash memory is insystem programmable and erasable. The last flash memory sector must contain a Customer Configuration section (CCFG) that is used by boot ROM and TI provided drivers to configure the device. This configuration is done through the ccfg.c source file that is included in all TI provided examples.

The ultra-low leakage system static RAM (SRAM) is split into up to five 16-KB blocks and can be used for both storage of data and execution of code. Retention of SRAM contents in Standby power mode is enabled by default and included in Standby mode power consumption numbers. Parity checking for detection of bit errors in memory is built-in, which reduces chip-level soft errors and thereby increases reliability. System SRAM is always initialized to zeroes upon code execution from boot.

To improve code execution speed and lower power when executing code from nonvolatile memory, a 4-way nonassociative 8-KB cache is enabled by default to cache and prefetch instructions read by the system CPU. The cache can be used as a general-purpose RAM by enabling this feature in the Customer Configuration Area (CCFG).

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There is a 4-KB ultra-low leakage SRAM available for use with the Sensor Controller Engine which is typically used for storing Sensor Controller programs, data and configuration parameters. This RAM is also accessible by the system CPU. The Sensor Controller RAM is not cleared to zeroes between system resets.

The ROM includes a TI-RTOS kernel and low-level drivers, as well as significant parts of selected radio stacks, which frees up flash memory for the application. The ROM also contains a serial (SPI and UART) bootloader that can be used for initial programming of the device.

9.5 Sensor Controller

The Sensor Controller contains circuitry that can be selectively enabled in both Standby and Active power modes. The peripherals in this domain can be controlled by the Sensor Controller Engine, which is a proprietary power-optimized CPU. This CPU can read and monitor sensors or perform other tasks autonomously; thereby significantly reducing power consumption and offloading the system CPU.

The Sensor Controller Engine is user programmable with a simple programming language that has syntax similar to C. This programmability allows for sensor polling and other tasks to be specified as sequential algorithms rather than static configuration of complex peripheral modules, timers, DMA, register programmable state machines, or event routing.

The main advantages are:

- Flexibility data can be read and processed in unlimited manners while still ensuring ultra-low power
- 2 MHz low-power mode enables lowest possible handling of digital sensors
- Dynamic reuse of hardware resources
- · 40-bit accumulator supporting multiplication, addition and shift
- Observability and debugging options

Sensor Controller Studio is used to write, test, and debug code for the Sensor Controller. The tool produces C driver source code, which the System CPU application uses to control and exchange data with the Sensor Controller. Typical use cases may be (but are not limited to) the following:

- Read analog sensors using integrated ADC or comparators
- Interface digital sensors using GPIOs, SPI, UART, or I²C (UART and I²C are bit-banged)
- Capacitive sensing
- · Waveform generation
- Very low-power pulse counting (flow metering)
- Key scan

The peripherals in the Sensor Controller include the following:

- The low-power clocked comparator can be used to wake the system CPU from any state in which the comparator is active. A configurable internal reference DAC can be used in conjunction with the comparator. The output of the comparator can also be used to trigger an interrupt or the ADC.
- Capacitive sensing functionality is implemented through the use of a constant current source, a time-to-digital converter, and a comparator. The continuous time comparator in this block can also be used as a higheraccuracy alternative to the low-power clocked comparator. The Sensor Controller takes care of baseline tracking, hysteresis, filtering, and other related functions when these modules are used for capacitive sensing.
- The ADC is a 12-bit, 200-ksamples/s ADC with eight inputs and a built-in voltage reference. The ADC can be triggered by many different sources including timers, I/O pins, software, and comparators.
- The analog modules can connect to up to eight different GPIOs
- Dedicated SPI master with up to 6 MHz clock speed

The peripherals in the Sensor Controller can also be controlled from the main application processor.

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9.6 Cryptography

The CC2642R device comes with a wide set of modern cryptography-related hardware accelerators, drastically reducing code footprint and execution time for cryptographic operations. It also has the benefit of being lower power and improves availability and responsiveness of the system because the cryptography operations runs in a background hardware thread.

Together with a large selection of open-source cryptography libraries provided with the Software Development Kit (SDK), this allows for secure and future proof IoT applications to be easily built on top of the platform. The hardware accelerator modules are:

- True Random Number Generator (TRNG) module provides a true, nondeterministic noise source for the purpose of generating keys, initialization vectors (IVs), and other random number requirements. The TRNG is built on 24 ring oscillators that create unpredictable output to feed a complex nonlinear-combinatorial circuit.
- Secure Hash Algorithm 2 (SHA-2) with support for SHA224, SHA256, SHA384, and SHA512
- Advanced Encryption Standard (AES) with 128 and 256 bit key lengths
- **Public Key Accelerator** Hardware accelerator supporting mathematical operations needed for elliptic curves up to 512 bits and RSA key pair generation up to 1024 bits.

Through use of these modules and the TI provided cryptography drivers, the following capabilities are available for an application or stack:

Key Agreement Schemes

- Elliptic curve Diffie Hellman with static or ephemeral keys (ECDH and ECDHE)
- Elliptic curve Password Authenticated Key Exchange by Juggling (ECJ-PAKE)

Signature Generation

- Elliptic curve Diffie-Hellman Digital Signature Algorithm (ECDSA)

Curve Support

- Short Weierstrass form (full hardware support), such as:
 - NIST-P224, NIST-P256, NIST-P384, NIST-P521
 - Brainpool-256R1, Brainpool-384R1, Brainpool-512R1
 - secp256r1
- Montgomery form (hardware support for multiplication), such as:
 - Curve25519

SHA2 based MACs

- HMAC with SHA224, SHA256, SHA384, or SHA512
- Block cipher mode of operation
 - AESCCM
 - AESGCM
 - AESECB
 - AESCBC
 - AESCBC-MAC

True random number generation

Other capabilities, such as RSA encryption and signatures as well as Edwards type of elliptic curves such as Curve1174 or Ed25519, can also be implemented using the provided hardware accelerators but are not part of the TI SimpleLink SDK for the CC2642R device.

Product Folder Links: CC2642R

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9.7 Timers

A large selection of timers are available as part of the CC2642R device. These timers are:

Real-Time Clock (RTC)

A 70-bit 3-channel timer running on the 32 kHz low frequency system clock (SCLK_LF) This timer is available in all power modes except Shutdown. The timer can be calibrated to compensate for frequency drift when using the LF RCOSC as the low frequency system clock. If an external LF clock with frequency different from 32.768 kHz is used, the RTC tick speed can be adjusted to compensate for this. When using TI-RTOS, the RTC is used as the base timer in the operating system and should thus only be accessed through the kernel APIs such as the Clock module. The real time clock can also be read by the Sensor Controller Engine to timestamp sensor data and also has dedicated capture channels. By default, the RTC halts when a debugger halts the device.

General Purpose Timers (GPTIMER)

The four flexible GPTIMERs can be used as either 4× 32 bit timers or 8× 16 bit timers, all running on up to 48 MHz. Each of the 16- or 32-bit timers support a wide range of features such as one-shot or periodic counting, pulse width modulation (PWM), time counting between edges and edge counting. The inputs and outputs of the timer are connected to the device event fabric, which allows the timers to interact with signals such as GPIO inputs, other timers, DMA and ADC. The GPTIMERs are available in Active and Idle power modes.

Sensor Controller Timers

The Sensor Controller contains 3 timers:

AUX Timer 0 and 1 are 16-bit timers with a 2^N prescaler. Timers can either increment on a clock or on each edge of a selected tick source. Both one-shot and periodical timer modes are available.

AUX Timer 2 is a 16-bit timer that can operate at 24 MHz, 2 MHz or 32 kHz independent of the Sensor Controller functionality. There are 4 capture or compare channels, which can be operated in one-shot or periodical modes. The timer can be used to generate events for the Sensor Controller Engine or the ADC, as well as for PWM output or waveform generation.

Radio Timer

A multichannel 32-bit timer running at 4 MHz is available as part of the device radio. The radio timer is typically used as the timing base in wireless network communication using the 32-bit timing word as the network time. The radio timer is synchronized with the RTC by using a dedicated radio API when the device radio is turned on or off. This ensures that for a network stack, the radio timer seems to always be running when the radio is enabled. The radio timer is in most cases used indirectly through the trigger time fields in the radio APIs and should only be used when running the accurate 48 MHz high frequency crystal is the source of SCLK HF.

Watchdog timer

The watchdog timer is used to regain control if the system operates incorrectly due to software errors. It is typically used to generate an interrupt to and reset of the device for the case where periodic monitoring of the system components and tasks fails to verify proper functionality. The watchdog timer runs on a 1.5 MHz clock rate and cannot be stopped once enabled. The watchdog timer pauses to run in Standby power mode and when a debugger halts the device.

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9.8 Serial Peripherals and I/O

The SSIs are synchronous serial interfaces that are compatible with SPI, MICROWIRE, and TI's synchronous serial interfaces. The SSIs support both SPI master and slave up to 4 MHz. The SSI modules support configurable phase and polarity.

The UARTs implement universal asynchronous receiver and transmitter functions. They support flexible baudrate generation up to a maximum of 3 Mbps.

The I²S interface is used to handle digital audio and can also be used to interface pulse-density modulation microphones (PDM).

The I²C interface is also used to communicate with devices compatible with the I²C standard. The I²C interface can handle 100 kHz and 400 kHz operation, and can serve as both master and slave.

The I/O controller (IOC) controls the digital I/O pins and contains multiplexer circuitry to allow a set of peripherals to be assigned to I/O pins in a flexible manner. All digital I/Os are interrupt and wake-up capable, have a programmable pullup and pulldown function, and can generate an interrupt on a negative or positive edge (configurable). When configured as an output, pins can function as either push-pull or open-drain. Five GPIOs have high-drive capabilities, which are marked in **bold** in † 7. All digital peripherals can be connected to any digital pin on the device.

For more information, see the CC13x2, CC26x2 SimpleLink™ Wireless MCU Technical Reference Manual.

9.9 Battery and Temperature Monitor

A combined temperature and battery voltage monitor is available in the CC2642R device. The battery and temperature monitor allows an application to continuously monitor on-chip temperature and supply voltage and respond to changes in environmental conditions as needed. The module contains window comparators to interrupt the system CPU when temperature or supply voltage go outside defined windows. These events can also be used to wake up the device from Standby mode through the Always-On (AON) event fabric.

9.10 uDMA

The device includes a direct memory access (µDMA) controller. The µDMA controller provides a way to offload data-transfer tasks from the system CPU, thus allowing for more efficient use of the processor and the available bus bandwidth. The µDMA controller can perform a transfer between memory and peripherals. The µDMA controller has dedicated channels for each supported on-chip module and can be programmed to automatically perform transfers between peripherals and memory when the peripheral is ready to transfer more data.

Some features of the µDMA controller include the following (this is not an exhaustive list):

- Highly flexible and configurable channel operation of up to 32 channels
- Transfer modes: memory-to-memory, memory-to-peripheral, peripheral-to-memory, and peripheral-to-peripheral
- Data sizes of 8, 16, and 32 bits
- Ping-pong mode for continuous streaming of data

9.11 Debug

The on-chip debug support is done through a dedicated cJTAG (IEEE 1149.7) or JTAG (IEEE 1149.1) interface. The device boots by default into cJTAG mode and must be reconfigured to use 4-pin JTAG.

Product Folder Links: CC2642R

Watchdog timer (WDT)

9.12 Power Management

To minimize power consumption, the CC2642R supports a number of power modes and power management features (see 表 9-1).

SOFTWARE CONFIGURABLE POWER MODES **RESET PIN** MODE **HELD ACTIVE IDLE STANDBY SHUTDOWN CPU** Off Off Off Active Off Flash Off Off On Available Off **SRAM** On On Retention Off Off Radio Available Available Off Off Off **Supply System** On On **Duty Cycled** Off Off Register and CPU retention Full Full Partial No No SRAM retention Full Full Full No No 48 MHz high-speed clock XOSC HF or XOSC HF or Off Off Off (SCLK HF) RCOSC HF RCOSC HF 2 MHz medium-speed clock RCOSC MF RCOSC MF Available Off Off (SCLK MF) 32 kHz low-speed clock XOSC LF or XOSC LF or XOSC LF or Off Off RCOSC LF RCOSC LF (SCLK LF) RCOSC LF Peripherals Available Available Off Off Off Sensor Controller Available Available Off Off Available Wake-up on RTC Off Available Available Available Off Wake-up on pin edge Available Available Available Available Off Wake-up on reset pin On On On On On On On Off Off Brownout detector (BOD) **Duty Cycled** Off Off Power-on reset (POR) On On On

表 9-1. Power Modes

In **Active** mode, the application system CPU is actively executing code. Active mode provides normal operation of the processor and all of the peripherals that are currently enabled. The system clock can be any available clock source (see $\frac{1}{8}$ 9-1).

Available

Paused

Off

Off

Available

In **Idle** mode, all active peripherals can be clocked, but the Application CPU core and memory are not clocked and no code is executed. Any interrupt event brings the processor back into active mode.

In **Standby** mode, only the always-on (AON) domain is active. An external wake-up event, RTC event, or Sensor Controller event is required to bring the device back to active mode. MCU peripherals with retention do not need to be reconfigured when waking up again, and the CPU continues execution from where it went into standby mode. All GPIOs are latched in standby mode.

In **Shutdown** mode, the device is entirely turned off (including the AON domain and Sensor Controller), and the I/Os are latched with the value they had before entering shutdown mode. A change of state on any I/O pin defined as a *wake from shutdown pin* wakes up the device and functions as a reset trigger. The CPU can differentiate between reset in this way and reset-by-reset pin or power-on reset by reading the reset status register. The only state retained in this mode is the latched I/O state and the flash memory contents.

The Sensor Controller is an autonomous processor that can control the peripherals in the Sensor Controller independently of the system CPU. This means that the system CPU does not have to wake up, for example to perform an ADC sampling or poll a digital sensor over SPI, thus saving both current and wake-up time that would otherwise be wasted. The Sensor Controller Studio tool enables the user to program the Sensor Controller, control its peripherals, and wake up the system CPU as needed. All Sensor Controller peripherals can also be controlled by the system CPU.

备注

The power, RF and clock management for the CC2642R device require specific configuration and handling by software for optimized performance. This configuration and handling is implemented in the TI-provided drivers that are part of the CC2642R software development kit (SDK). Therefore, TI highly recommends using this software framework for all application development on the device. The complete SDK with TI-RTOS (optional), device drivers, and examples are offered free of charge in source code.

9.13 Clock Systems

The CC2642R device has several internal system clocks.

The 48 MHz SCLK_HF is used as the main system (MCU and peripherals) clock. This can be driven by the internal 48 MHz RC Oscillator (RCOSC_HF) or an external 48 MHz crystal (XOSC_HF). Radio operation requires an external 48 MHz crystal.

SCLK_MF is an internal 2 MHz clock that is used by the Sensor Controller in low-power mode and also for internal power management circuitry. The SCLK_MF clock is always driven by the internal 2 MHz RC Oscillator (RCOSC_MF).

SCLK_LF is the 32.768 kHz internal low-frequency system clock. It can be used by the Sensor Controller for ultra-low-power operation and is also used for the RTC and to synchronize the radio timer before or after Standby power mode. SCLK_LF can be driven by the internal 32.8 kHz RC Oscillator (RCOSC_LF), a 32.768 kHz watch-type crystal, or a clock input on any digital IO.

When using a crystal or the internal RC oscillator, the device can output the 32 kHz SCLK_LF signal to other devices, thereby reducing the overall system cost.

9.14 Network Processor

Depending on the product configuration, the CC2642R device can function as a wireless network processor (WNP - a device running the wireless protocol stack with the application running on a separate host MCU), or as a system-on-chip (SoC) with the application and protocol stack running on the system CPU inside the device.

In the first case, the external host MCU communicates with the device using SPI or UART. In the second case, the application must be written according to the application framework supplied with the wireless protocol stack.

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10 Application, Implementation, and Layout

备注

以下应用部分中的信息不属于 TI 器件规格的范围, TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

For general design guidelines and hardware configuration guidelines, refer to the CC13xx/CC26xx Hardware Configuration and PCB Design Considerations Application Report.

10.1 Reference Designs

The following reference designs should be followed closely when implementing designs using the CC2642R device.

Special attention must be paid to RF component placement, decoupling capacitors and DCDC regulator components, as well as ground connections for all of these.

Integrated matched filter-balun devices can be used both at sub-1 GHz frequencies and at 2.4 GHz for the low-power RF outputs. Refer to the "Integrated Passive Component" section in CC13xx/CC26xx Hardware Configuration and PCB Design Considerations for further information.

CC26x2REM-7ID Design Files

The CC26x2REM-7ID reference design provides schematic, layout and production files for the characterization board used for deriving the performance number found in this document.

LAUNCHXL-CC26X2R1 Design Files

The CC26X2R LaunchPad Design Files contain detailed schematics and layouts to build application specific boards using the CC2642R device. This design applies to both the CC2642R and CC2652R devices.

Sub-1 GHz and 2.4 GHz Antenna Kit for LaunchPad ™ Development Kit and SensorTag The antenna kit allows real-life testing to identify the optimal antenna for your application. The antenna kit includes 16 antennas for frequencies from 169 MHz to 2.4 GHz, including:

- PCB antennas
- · Helical antennas
- · Chip antennas
- Dual-band antennas for 868 MHz and 915 MHz combined with 2.4 GHz

The antenna kit includes a JSC cable to connect to the Wireless MCU LaunchPad development kits and SensorTags.

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10.2 Junction Temperature Calculation

This section shows the different techniques for calculating the junction temperature under various operating conditions. For more details, see Semiconductor and IC Package Thermal Metrics.

There are three recommended ways to derive the junction temperature from other measured temperatures:

1. From package temperature:

$$T_I = \psi_{\text{IT}} \times P + T_{\text{case}} \tag{1}$$

2. From board temperature:

$$T_I = \psi_{\rm IB} \times P + T_{\rm board} \tag{2}$$

3. From ambient temperature:

$$T_I = R_{\theta IA} \times P + T_A \tag{3}$$

P is the power dissipated from the device and can be calculated by multiplying current consumption with supply voltage. Thermal resistance coefficients are found in *Thermal Resistance Characteristics*.

Example:

Using 方程式 3, the temperature difference between ambient temperature and junction temperature is calculated. In this example, we assume a simple use case where the radio is transmitting continuously at 0 dBm output power. Let us assume the ambient temperature is 85 °C and the supply voltage is 3 V. To calculate P, we need to look up the current consumption for Tx at 85 °C in \dagger 8.14. From the plot, we see that the current consumption is 7.8 mA. This means that P is 7.8 mA × 3 V = 23.4 mW.

The junction temperature is then calculated as:

$$T_I = 23.4^{\circ} C/_W \times 23.4 mW + T_A = 0.6^{\circ} C + T_A$$
 (4)

As can be seen from the example, the junction temperature is 0.6 °C higher than the ambient temperature when running continuous Tx at 85 °C and, thus, well within the recommended operating conditions.

For various application use cases current consumption for other modules may have to be added to calculate the appropriate power dissipation. For example, the MCU may be running simultaneously as the radio, peripheral modules may be enabled, etc. Typically, the easiest way to find the peak current consumption, and thus the peak power dissipation in the device, is to measure as described in Measuring CC13xx and CC26xx current consumption.

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11 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed as follows.

11.1 Tools and Software

The CC2642R device is supported by a variety of software and hardware development tools.

Development Kit

CC26x2 LaunchPad™ Development Kit

The CC26x2R LaunchPad ™ Development Kit enables development of high-performance wireless applications that benefit from low-power operation. The kit features the CC2652R SimpleLink Wireless MCU, which allows you to quickly evaluate and prototype 2.4-GHz wireless applications such as Bluetooth 5 Low Energy, Zigbee and Thread, plus combinations of these. The kit works with the LaunchPad ecosystem, easily enabling additional functionality like sensors, display and more. The built-in EnergyTrace™ software is an energy-based code analysis tool that measures and displays the application's energy profile and helps to optimize it for ultra-low-power consumption. See 表 6-1 for guidance in selecting the correct device for single-protocol products.

Software

SimpleLink™ CC13x2-CC26x2 SDK

The SimpleLink CC13x2-CC26x2 Software Development Kit (SDK) provides a complete package for the development of wireless applications on the CC13x2 / CC26x2 family of devices. The SDK includes a comprehensive software package for the CC2642R device, including the following protocol stacks:

- Bluetooth Low Energy 4 and 5.2
- Thread (based on OpenThread)
- Zigbee 3.0
- TI 15.4-Stack an IEEE 802.15.4-based star networking solution for Sub-1 GHz and 2.4 GHz
- EasyLink a large set of building blocks for building proprietary RF software stacks
- Multiprotocol support concurrent operation between stacks using the Dynamic Multiprotocol Manager (DMM)

The SimpleLink CC13x2-CC26x2 SDK is part of TI's SimpleLink MCU platform, offering a single development environment that delivers flexible hardware, software and tool options for customers developing wired and wireless applications. For more information about the SimpleLink MCU Platform, visit https://www.ti.com/simplelink.



Development Tools

Code Composer Studio™ Integrated Development Environment (IDE)

Code Composer Studio is an integrated development environment (IDE) that supports TI's Microcontroller and Embedded Processors portfolio. Code Composer Studio comprises a suite of tools used to develop and debug embedded applications. It includes an optimizing C/C++ compiler, source code editor, project build environment, debugger, profiler, and many other features. The intuitive IDE provides a single user interface taking you through each step of the application development flow. Familiar tools and interfaces allow users to get started faster than ever before. Code Composer Studio combines the advantages of the Eclipse® software framework with advanced embedded debug capabilities from TI resulting in a compelling feature-rich development environment for embedded developers.

CCS has support for all SimpleLink Wireless MCUs and includes support for EnergyTrace™ software (application energy usage profiling). A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK.

Code Composer Studio is provided free of charge when used in conjunction with the XDS debuggers included on a LaunchPad Development Kit.

Code Composer Studio™ Cloud IDE

Code Composer Studio (CCS) Cloud is a web-based IDE that allows you to create, edit and build CCS and Energia[™] projects. After you have successfully built your project, you can download and run on your connected LaunchPad. Basic debugging, including features like setting breakpoints and viewing variable values is now supported with CCS Cloud.

IAR Embedded Workbench® for Arm®

IAR Embedded Workbench[®] is a set of development tools for building and debugging embedded system applications using assembler, C and C++. It provides a completely integrated development environment that includes a project manager, editor, and build tools. IAR has support for all SimpleLink Wireless MCUs. It offers broad debugger support, including XDS110, IAR I-jet[™] and Segger J-Link [™]. A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK. IAR is also supported out-of-the-box on most software examples provided as part of the SimpleLink SDK.

A 30-day evaluation or a 32 KB size-limited version is available through jar.com.

SmartRF™ Studio

SmartRF™ Studio is a Windows® application that can be used to evaluate and configure SimpleLink Wireless MCUs from Texas Instruments. The application will help designers of RF systems to easily evaluate the radio at an early stage in the design process. It is especially useful for generation of configuration register values and for practical testing and debugging of the RF system. SmartRF Studio can be used either as a standalone application or together with applicable evaluation boards or debug probes for the RF device. Features of the SmartRF Studio include:

- Link tests send and receive packets between nodes
- · Antenna and radiation tests set the radio in continuous wave TX and RX states
- Export radio configuration code for use with the TI SimpleLink SDK RF driver
- Custom GPIO configuration for signaling and control of external switches

Sensor Controller Studio

Sensor Controller Studio is used to write, test and debug code for the Sensor Controller peripheral. The tool generates a Sensor Controller Interface driver, which is a set of C source files that are compiled into the System CPU application. These source files also contain the Sensor Controller binary image and allow the System CPU application to control and exchange data with the Sensor Controller. Features of the Sensor Controller Studio include:

- Ready-to-use examples for several common use cases
- Full toolchain with built-in compiler and assembler for programming in a C-like programming language
- Provides rapid development by using the integrated sensor controller task testing and debugging functionality, including visualization of sensor data and verification of algorithms

CCS UniFlash

CCS UniFlash is a standalone tool used to program on-chip flash memory on TI MCUs. UniFlash has a GUI, command line, and scripting interface. CCS UniFlash is available free of charge.

11.1.1 SimpleLink™ Microcontroller Platform

The SimpleLink microcontroller platform sets a new standard for developers with the broadest portfolio of wired and wireless Arm® MCUs (System-on-Chip) in a single software development environment. Delivering flexible hardware, software and tool options for your IoT applications. Invest once in the SimpleLink software development kit and use throughout your entire portfolio. Learn more on ti.com/simplelink.

11.2 Documentation Support

To receive notification of documentation updates on data sheets, errata, application notes and similar, navigate to the device product folder on ti.com/product/CC2642R. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

The current documentation that describes the MCU, related peripherals, and other technical collateral is listed as follows.

TI Resource Explorer

TI Resource Explorer Software examples, libraries, executables, and documentation are available for your device and development board.

Errata

CC2642R Silicon Errata

The silicon errata describes the known exceptions to the functional specifications for each silicon revision of the device and description on how to recognize a device revision.

Application Reports

All application reports for the CC2642R device are found on the device product folder at: ti.com/product/ CC2642R/technicaldocuments.

Technical Reference Manual (TRM)

CC13x2, CC26x2 SimpleLink™ Wireless MCU TRM

The TRM provides a detailed description of all modules and peripherals available in the device family.

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11.3 支持资源

TI E2E[™] 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

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ESD 的损坏小至导致微小的性能降级,大至整个器件故障。精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.6 术语表

TI术语表本术语表列出并解释了术语、首字母缩略词和定义。

12 Mechanical, Packaging, and Orderable Information 12.1 Packaging Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CC2642R1FRGZR	ACTIVE	VQFN	RGZ	48	2500	RoHS & Green	NIPDAU NIPDAUAG	Level-3-260C-168 HR	-40 to 105	CC2642 R1F	Samples
CC2642R1FRGZT	ACTIVE	VQFN	RGZ	48	250	RoHS & Green	NIPDAU NIPDAUAG	Level-3-260C-168 HR	-40 to 105	CC2642 R1F	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF CC2642R:

Automotive : CC2642R-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CC2642R1FRGZR	VQFN	RGZ	48	2500	330.0	16.4	7.3	7.3	1.1	12.0	16.0	Q2
CC2642R1FRGZT	VQFN	RGZ	48	250	180.0	16.4	7.3	7.3	1.1	12.0	16.0	Q2

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CC2642R1FRGZR	VQFN	RGZ	48	2500	367.0	367.0	35.0
CC2642R1FRGZT	VQFN	RGZ	48	250	210.0	185.0	35.0

7 x 7, 0.5 mm pitch

PLASTIC QUADFLAT PACK- NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224671/A



PLASTIC QUADFLAT PACK- NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUADFLAT PACK- NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUADFLAT PACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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